

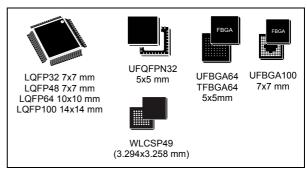
# STM32L071x8 STM32L071xB STM32L071xZ

Access line ultra-low-power 32-bit MCU Arm<sup>®</sup>-based Cortex<sup>®</sup>-M0+, up to 192KB Flash, 20KB SRAM, 6KB EEPROM, ADC

Datasheet - production data

### **Features**

- Ultra-low-power platform
  - 1.65 V to 3.6 V power supply
  - -40 to 125 °C temperature range
  - 0.29 μA Standby mode (3 wakeup pins)
  - 0.43 µA Stop mode (16 wakeup lines)
  - 0.86 µA Stop mode + RTC + 20 KB RAM retention
  - Down to 93 µA/MHz in Run mode
  - 5 µs wakeup time (from Flash memory)
  - 41 μA 12-bit ADC conversion at 10 ksps
- Core: Arm<sup>®</sup> 32-bit Cortex<sup>®</sup>-M0+ with MPU
  - From 32 kHz up to 32 MHz max.
  - 0.95 DMIPS/MHz
- Memories
  - Up to 192 KB Flash memory with ECC(2 banks with read-while-write capability)
  - 20 KB RAM
  - 6 KB of data EEPROM with ECC
  - 20-byte backup register
  - Sector protection against R/W operation
- Up to 84 fast I/Os (78 I/Os 5V tolerant)
- · Reset and supply management
  - Ultra-safe, low-power BOR (brownout reset) with 5 selectable thresholds
  - Ultra-low-power POR/PDR
  - Programmable voltage detector (PVD)
- Clock sources
  - 1 to 25 MHz crystal oscillator
  - 32 kHz oscillator for RTC with calibration
  - High speed internal 16 MHz factory-trimmed RC (+/- 1%)
  - Internal low-power 37 kHz RC
  - Internal multispeed low-power 65 kHz to 4.2 MHz RC
  - PLL for CPU clock
- Pre-programmed bootloader
  - USART, I2C, SPI supported
- Development support
  - Serial wire debug supported



- Rich Analog peripherals
  - 12-bit ADC 1.14 Msps up to 16 channels (down to 1.65 V)
  - 2x ultra-low-power comparators (window mode and wake up capability, down to 1.65 V)
- 7-channel DMA controller, supporting ADC, SPI, I2C, USART, Timers
- Up to 10x peripheral communication interfaces
  - 4x USART (2 with ISO 7816, IrDA), 1x UART (low power)
  - Up to 6x SPI 16 Mbits/s
  - 3x I2C (2 with SMBus/PMBus)
- 11x timers: 2x 16-bit with up to 4 channels, 2x 16-bit with up to 2 channels, 1x 16-bit ultra-low-power timer, 1x SysTick, 1x RTC, 2x 16-bit basic, and 2x watchdogs (independent/window)
- CRC calculation unit, 96-bit unique ID
- All packages are ECOPACK<sup>®</sup>2

Table 1. Device summary

Reference	Part number
STM32L071x8	STM32L071V8, STM32L071K8, STM32L071C8
STM32L071xB	STM32L071VB, STM32L071RB, STM32L071CB, STM32L071KB
STM32L071xZ	STM32L071VZ, STM32L071RZ, STM32L071CZ, STM32L071KZ

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STM32L071xx Introduction

# 1 Introduction

The ultra-low-power STM32L071xx are offered in 9 different package types from 32 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L071xx microcontrollers suitable for a wide range of applications:

- Gas/water meters and industrial sensors
- Healthcare and fitness equipment
- · Remote control and user interface
- PC peripherals, gaming, GPS equipment
- Alarm system, wired and wireless sensors, video intercom

This STM32L071xx datasheet should be read in conjunction with the STM32L0x1xx reference manual (RM0377).

For information on the Arm<sup>®</sup> Cortex<sup>®</sup>-M0+ core please refer to the Cortex<sup>®</sup>-M0+ Technical Reference Manual, available from the www.arm.com website.

Figure 1 shows the general block diagram of the device family.

Description STM32L071xx

# 2 Description

The access line ultra-low-power STM32L071xx microcontrollers incorporate the high-performance Arm<sup>®</sup> Cortex<sup>®</sup>-M0+ 32-bit RISC core operating at a 32 MHz frequency, a memory protection unit (MPU), high-speed embedded memories (up to 192 Kbytes of Flash program memory, 6 Kbytes of data EEPROM and 20 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L071xx devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L071xx devices offer several analog features, one 12-bit ADC with hardware oversampling, two ultra-low-power comparators, several timers, one low-power timer (LPTIM), four general-purpose 16-bit timers and two basic timer, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L071xx devices embed standard and advanced communication interfaces: up to three I2Cs, two SPIs, one I2S, four USARTs, a low-power UART (LPUART), .

The STM32L071xx also include a real-time clock and a set of backup registers that remain powered in Standby mode.

The ultra-low-power STM32L071xx devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.





STM32L071xx Description

# 2.1 Device overview

Table 2. Ultra-low-power STM32L071xx device features and peripheral counts

Flash (Kbytes)   64 Kbytes   128 Kbytes   192 Kbytes			
RAM (Kbytes)   20 Kbytes   4			
Timers			
Purpose   Basic   2			
RTC/SYSTICK/IWDG			
RTC/SYSTICK/IWDG			
SPI/I2S   4(3)(1)/0   6(4)(2)/1   4(3)(1)/0   6(4)(2)/1   4(3)(1)/0   6(4)(2)/1   4(3)(1)/0   6(4)(2)/1     1/2			
Com. interfaces         I²C         2         3         2         3         2         3           USART         3         4         4(3)         4         4(3)         4         4(3)         4         4         4(3)         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4         4			
Com.			
USART 3 4 4(3) 4 4(3) 4  LPUART 1  GPIOs 23 37 84 25(3) 40(4) 84 51(5) 25(3) 40(4) 84  Clocks: HSE/LSE/HSI/MSI/LSI  42 bit synchronized			
GPIOs 23 37 84 25 <sup>(3)</sup> 40 <sup>(4)</sup> 84 51 <sup>(5)</sup> 25 <sup>(3)</sup> 40 <sup>(4)</sup> 84  Clocks: HSE/LSE/HSI/MSI/LSI  1/1/1/1/1			
Clocks: HSE/LSE/HSI/MSI/LSI  1/1/1/1/1  12 hit synchronized			
HSE/LSE/HSI/MSI/LSI  17/1/1/1/1  13 bit synchronized	51 <sup>(5)</sup>		
12-bit synchronized			
ADC Number of channels 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 16 <sup>(5)</sup>		
Comparators 2			
Max. CPU frequency 32 MHz			
perating voltage 1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 to 3.6 V without BOR option			
Operating Ambient temperature: -40 to +125 °C temperatures Junction temperature: -40 to +130 °C			
Packages         UFQFPN 32         LQFP48         LQFP/ UFBGA 100         UFQFPN/ LQFP32         LQFP48, WLCSP49         LQFP/ UFBGA 100         LQFP/ LQFP32         UFQFPN/ LQFP32         LQFP48, WLCSP49         LQFP/ LQFP32         UFQFPN/ LQFP32         LQFP48, WLCSP49         LQFP32         UFQFPN/ LQFP32         LQFP48, WLCSP49         LQFP32         LQFP32			

<sup>1. 3</sup> SPI interfaces are USARTs operating in SPI master mode.

<sup>2. 4</sup> SPI interfaces are USARTs operating in SPI master mode.

<sup>3.</sup> UFQFPN32 has 2 GPIOs and 1 UART less than LQFP32.

<sup>4.</sup> LQFP48 has three GPIOs less than WLCSP49.

<sup>5.</sup> TFBGA64 has one GPIO, one ADC input less than LQFP64.

Description STM32L071xx

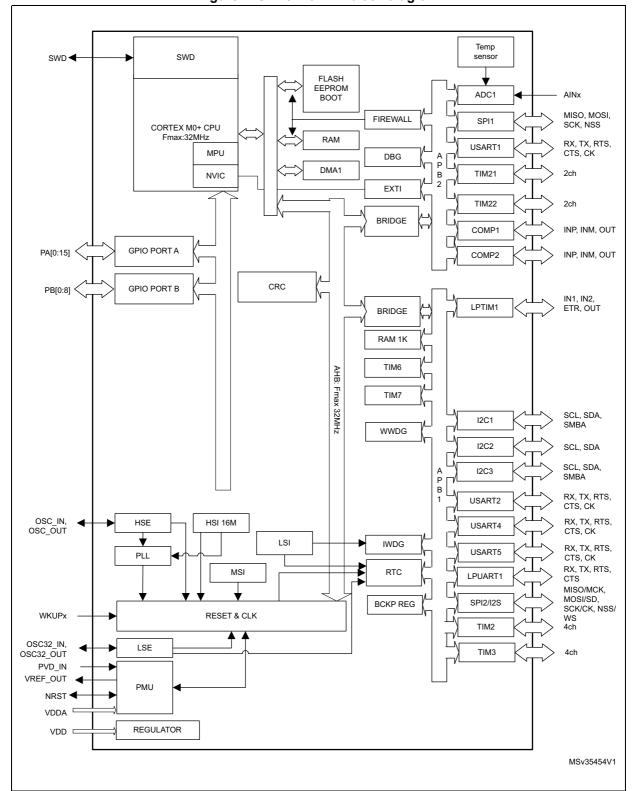


Figure 1. STM32L071xx block diagram



STM32L071xx Description

# 2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to Arm® Cortex®-M4, including Arm® Cortex®-M3 and Arm® Cortex®-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 ultra-low-power series are the best solution for applications such as gaz/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.



# 3 Functional overview

# 3.1 Low-power modes

The ultra-low-power STM32L071xx support dynamic voltage scaling to optimize its power consumption in Run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V<sub>DD</sub> range limited to 1.71-3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V<sub>DD</sub> range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V<sub>DD</sub> range), with a maximum CPU frequency limited to 4.2 MHz

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

#### Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.

#### Low-power run mode

This mode is achieved with the multispeed internal (MSI) RC oscillator set to the low-speed clock (max 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In Low-power run mode, the clock frequency and the number of enabled peripherals are both limited.

### Low-power sleep mode

This mode is achieved by entering Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

When wakeup is triggered by an event or an interrupt, the system reverts to the Run mode with the regulator on.

#### Stop mode with RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the  $V_{CORE}$  domain are stopped, the PLL, MSI RC, HSE crystal and HSI RC oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on), it can be the RTC alarm/tamper/timestamp/wakeup events, the USART/I2C/LPUART/LPTIMER wakeup events.



#### Stop mode without RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5  $\mu$ s, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USART/I2C/LPUART/LPTIMER wakeup events.

#### Standby mode with RTC

The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire  $V_{CORE}$  domain is powered off. The PLL, MSI RC, HSE crystal and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC CSR register).

The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

#### Standby mode without RTC

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire  $V_{CORE}$  domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC\_CSR register).

The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note:

The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

Table 3. Functionalities depending on the operating power supply range

Operating power supply range <sup>(1)</sup>	Functionalities depending on the operating power supply range	
Operating power supply range	ADC operation	Dynamic voltage scaling range
V <sub>DD</sub> = 1.65 to 1.71 V	ADC only, conversion time up to 570 ksps	Range 2 or range 3
V <sub>DD</sub> = 1.71 to 1.8 V <sup>(2)</sup>	ADC only, conversion time up to 1.14 Msps	Range 1, range 2 or range 3
V <sub>DD</sub> = 1.8 to 2.0 V <sup>(2)</sup>	Conversion time up to 1.14 Msps	Range1, range 2 or range 3



Table 3. Functionalities depending on the operating power supply range (continued)

Operating power supply range <sup>(1)</sup>	Functionalities depending on the operating power supply range	
Operating power supply range	ADC operation	Dynamic voltage scaling range
V <sub>DD</sub> = 2.0 to 2.4 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3
V <sub>DD</sub> = 2.4 to 3.6 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3

GPIO speed depends on V<sub>DD</sub> voltage. Refer to *Table 60: I/O AC characteristics* for more information about I/O speed.

Table 4. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
32 kHz to 4.2 MHz (0ws)	Range 3

Table 5. Functionalities depending on the working mode (from Run/active down to standby) <sup>(1)(2)</sup>

			Low-	Low-		Stop	9	Standby
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
CPU	Y		Y					
Flash memory	0	0	0	0			-	
RAM	Y	Y	Y	Y	Υ			
Backup registers	Y	Y	Y	Y	Υ		Υ	
EEPROM	0	0	0	0	-		-	
Brown-out reset (BOR)	0	0	0	0	0	0	0	0
DMA	0	0	0	0			-	
Programmable Voltage Detector (PVD)	0	0	0	0	0	0	-	
Power-on/down reset (POR/PDR)	Y	Y	Y	Y	Υ	Y	Y	Y

<sup>2.</sup> CPU frequency changes from initial to final must respect "fcpu initial <4\*fcpu final". It must also respect 5  $\mu s$  delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2 MHz to 16 MHz, wait 5  $\mu s$ , then switch from 16 MHz to 32 MHz.

Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued) $^{(1)(2)}$ 

			Low-	Low-		Stop	Standby	
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
High Speed Internal (HSI)	0	0			(3)			
High Speed External (HSE)	0	0	0	0				
Low Speed Internal (LSI)	0	0	0	0	0		0	
Low Speed External (LSE)	0	О	0	0	0		0	
Multi-Speed Internal (MSI)	0	О	Y	Y				
Inter-Connect Controller	Υ	Y	Y	Y	Υ			
RTC	0	0	0	0	0	0	0	
RTC Tamper	0	0	0	0	0	0	0	0
Auto WakeUp (AWU)	0	0	0	0	0	0	0	0
USART	0	0	0	0	O <sup>(4)</sup>	0		
LPUART	0	0	0	0	O <sup>(4)</sup>	0		
SPI	0	0	0	0				
I2C	0	0	0	0	O <sup>(5)</sup>	0	-	
ADC	0	0					-	
Temperature sensor	0	0	0	0	0			
Comparators	0	0	0	0	0	0	-	
16-bit timers	0	0	0	0				
LPTIMER	0	0	0	0	0	0		
IWDG	0	0	0	0	0	0	0	0
WWDG	0	0	0	0				
SysTick Timer	0	0	0	0			-	
GPIOs	0	0	0	0	0	0		2 pins
Wakeup time to Run mode	0 µs	0.36 μs	3 µs	32 µs	3.5 µs			50 μs

Table 5. Functionalities depending on the working mode
(from Run/active down to standby) (continued) <sup>(1)(2)</sup>

			Low-	Low-	Stop		Stop Standby		
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability	
				Down to 8 μA			4 μΑ (No V <sub>DD</sub> =1.8 V		
Consumption V <sub>DD</sub> =1.8 to 3.6 V	Down to 140 µA/MHz	Down to 37 µA/MHz					μΑ (with V <sub>DD</sub> =1.8 V		1 \
(Typ)	(from Flash memory)	(from Flash memory)					4 μA (No V <sub>DD</sub> =3.0 V	0.65 μA (with / RTC) V <sub>DD</sub> =1.8 V 0.29 μA (No / RTC) V <sub>DD</sub> =3.0 V	
						(with RTC) <sub>DD</sub> =3.0 V		5 μA (with ) V <sub>DD</sub> =3.0 V	

Legend:

- 2. The consumption values given in this table are preliminary data given for indication. They are subject to slight changes.
- 3. Some peripherals with wakeup from Stop capability can request HSI to be enabled. In this case, HSI is woken up by the peripheral, and only feeds the peripheral which requested it. HSI is automatically put off when the peripheral does not need it anymore.
- 4. UART and LPUART reception is functional in Stop mode. It generates a wakeup interrupt on Start. To generate a wakeup on address match or received frame event, the LPUART can run on LSE clock while the UART has to wake up or keep running the HSI clock.
- 5. I2C address detection is functional in Stop mode. It generates a wakeup interrupt in case of address match. It will wake up the HSI during reception.

#### 3.2 Interconnect matrix

Several peripherals are directly interconnected. This allows autonomous communication between peripherals, thus saving CPU resources and power consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, Low-power run, Low-power sleep and Stop modes.

Table 6. STM32L0xx peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low- power run	Low- power sleep	Stop
COMPx	TIM2,TIM21, TIM22	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Y	ı
COMIX	LPTIM	Timer input channel, trigger from analog signals comparison	Y	Y	Y	Υ	Y
TIMx	TIMx	Timer triggered by other timer		Y	Υ	-	



<sup>&</sup>quot;Y" = Yes (enable).
"O" = Optional can be enabled/disabled by software)
"-" = Not available

Low-Low-Interconnect Interconnect Interconnect action Run Sleep power power Stop destination source run sleep Timer triggered by Auto TIM21 Υ Υ Υ Υ wake-up **RTC** Timer triggered by RTC **LPTIM** Υ Υ Υ Υ Υ event Clock source used as All clock input channel for RC TIMx Υ Υ Υ Υ source measurement and trimming Timer input channel and Υ Υ TIMx Υ Υ trigger **GPIO** Timer input channel and **LPTIM** Υ Υ Υ Υ Υ trigger Conversion trigger **ADC** Υ Υ Υ Υ

Table 6. STM32L0xx peripherals interconnect matrix (continued)

# 3.3 Arm<sup>®</sup> Cortex<sup>®</sup>-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit Arm Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- · deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded Arm core, the STM32L071xx are compatible with all Arm tools and software.

### **Nested vectored interrupt controller (NVIC)**

The ultra-low-power STM32L071xx embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- · provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

# 3.4 Reset and supply management

# 3.4.1 Power supply schemes

- V<sub>DD</sub> = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V<sub>DD</sub> pins.
- V<sub>SSA</sub>, V<sub>DDA</sub> = 1.65 to 3.6 V: external analog power supplies for ADC reset blocks, RCs and PLL. V<sub>DDA</sub> and V<sub>SSA</sub> must be connected to V<sub>DD</sub> and V<sub>SS</sub>, respectively.

### 3.4.2 Power supply supervisor

The devices have an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the  $V_{DD}$  threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on  $V_{DD}$  at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the

internal reference voltage ( $V_{REFINT}$ ) in Stop mode. The device remains in reset mode when  $V_{DD}$  is below a specified threshold,  $V_{POR/PDR}$  or  $V_{BOR}$ , without the need for any external reset circuit.

Note:

The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The devices feature an embedded programmable voltage detector (PVD) that monitors the  $V_{DD/VDDA}$  power supply and compares it to the  $V_{PVD}$  threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when  $V_{DD/VDDA}$  drops below the  $V_{PVD}$  threshold and/or when  $V_{DD/VDDA}$  is higher than the  $V_{PVD}$  threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

### 3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32 KHz oscillator, RCC\_CSR).

# 3.5 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

### Clock prescaler

To get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.

#### Safe clock switching

Clock sources can be changed safely on the fly in Run mode through a configuration register.

#### Clock management

To reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.

#### System clock source

Three different clock sources can be used to drive the master clock SYSCLK:

- 1-25 MHz high-speed external crystal (HSE), that can supply a PLL
- 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLLMultispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz). When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.

# Auxiliary clock source

Two ultra-low-power clock sources that can be used to drive the real-time clock:



- 32.768 kHz low-speed external crystal (LSE)
- 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog.
   The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.

#### RTC clock source

The LSI, LSE or HSE sources can be chosen to clock the RTC, whatever the system clock.

### Startup clock

After reset, the microcontroller restarts by default with an internal 2.1 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

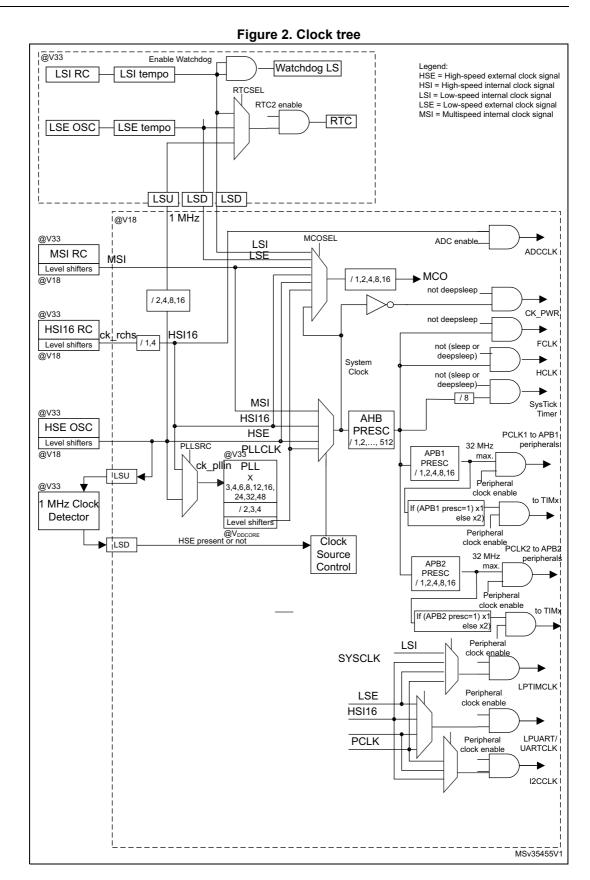
### Clock security system (CSS)

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled. Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.

# Clock-out capability (MCO: microcontroller clock output)

It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.



# 3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

# 3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

### **Extended interrupt/event controller (EXTI)**

The extended interrupt/event controller consists of 29 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 84 GPIOs can be connected to the 16 configurable interrupt/event lines. The 13 other lines are connected to PVD, RTC, USARTS, I2C, LPUART, LPTIMER or comparator events.



# 3.8 Memories

The STM32L071xx devices have the following features:

 20 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).

- The non-volatile memory is divided into three arrays:
  - 64, 128 or 192 Kbytes of embedded Flash program memory
  - 6 Kbytes of data EEPROM
  - Information block containing 32 user and factory options bytes plus 8 Kbytes of system memory

Flash program and data EEPROM are divided into two banks. This allows writing in one bank while running code or reading data from the other bank.

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no protection
- Level 1: memory readout protected.
  - The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- **Level 2**: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (Flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

# 3.9 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1(PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), I2C1 (PB6, PB7) or I2C2 (PB10, PB11), USART1(PA9, PA10) or USART2(PA2, PA3). See STM32™ microcontroller system memory boot mode AN2606 for details.

# 3.10 Direct memory access (DMA)

The flexible 7-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I<sup>2</sup>C, USART, LPUART, general-purpose timers, and ADC.

# 3.11 Analog-to-digital converter (ADC)

A native 12-bit, extended to 16-bit through hardware oversampling, analog-to-digital converter is embedded into STM32L071xx device. It has up to 16 external channels and 3 internal channels (temperature sensor, voltage reference). Three channels, PA0, PA4 and PA5, are fast channels, while the others are standard channels.

The ADC performs conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC frequency is independent from the CPU frequency, allowing maximum sampling rate of 1.14 MSPS even with a low CPU speed. The ADC consumption is low at all frequencies ( $\sim$ 25  $\mu$ A at 10 kSPS,  $\sim$ 240  $\mu$ A at 1MSPS). An auto-shutdown function guarantees that the ADC is powered off except during the active conversion phase.

The ADC can be served by the DMA controller. It can operate from a supply voltage down to 1.65 V.

The ADC features a hardware oversampler up to 256 samples, this improves the resolution to 16 bits (see AN2668).

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers.

# 3.12 Temperature sensor

The temperature sensor ( $T_{SENSE}$ ) generates a voltage  $V_{SENSE}$  that varies linearly with temperature.

The temperature sensor is internally connected to the ADC\_IN18 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Calibration value name	Description	Memory address
TSENSE_CAL1	TS ADC raw data acquired at temperature of 30 °C, V <sub>DDA</sub> = 3 V	0x1FF8 007A - 0x1FF8 007B
TSENSE_CAL2	TS ADC raw data acquired at temperature of 130 °C V <sub>DDA</sub> = 3 V	0x1FF8 007E - 0x1FF8 007F

Table 7. Temperature sensor calibration values

# 3.12.1 Internal voltage reference (V<sub>REFINT</sub>)

The internal voltage reference ( $V_{REFINT}$ ) provides a stable (bandgap) voltage output for the ADC and Comparators.  $V_{REFINT}$  is internally connected to the ADC\_IN17 input channel. It enables accurate monitoring of the  $V_{DD}$  value (when no external voltage,  $V_{REF+}$ , is available for ADC). The precise voltage of  $V_{REFINT}$  is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 8. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V <sub>DDA</sub> = 3 V	0x1FF8 0078 - 0x1FF8 0079

# 3.13 Ultra-low-power comparators and reference voltage

The STM32L071xx embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
  - External I/O pins
  - Internal reference voltage (V<sub>REFINT</sub>)
  - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 µA typical).

# 3.14 Timers and watchdogs

The ultra-low-power STM32L071xx devices include three general-purpose timers, one low-power timer (LPTIM), one basic timer, two watchdog timers and the SysTick timer.

Table 9 compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21, TIM22	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

Table 9. Timer feature comparison

### 3.14.1 General-purpose timers (TIM2, TIM3, TIM21 and TIM22)

There are four synchronizable general-purpose timers embedded in the STM32L071xx device (see *Table 9* for differences).

### TIM2, TIM3

TIM2 and TIM3 are based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2/TIM3 general-purpose timers can work together or with the TIM21 and TIM22 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2/TIM3 have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

#### TIM21 and TIM22

TIM21 and TIM22 are based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. They have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together and be synchronized with the TIM2/TIM3, full-featured general-purpose timers.

They can also be used as simple time bases and be clocked by the LSE clock source (32.768 kHz) to provide time bases independent from the main CPU clock.

# 3.14.2 Low-power Timer (LPTIM)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- · Configurable output: pulse, PWM
- Continuous / one shot mode
- Selectable software / hardware input trigger
- Selectable clock source
  - Internal clock source: LSE, LSI, HSI or APB clock
  - External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

# 3.14.3 Basic timer (TIM6, TIM7)

These timers can be used as a generic 16-bit timebase.

# 3.14.4 SysTick timer

This timer is dedicated to the OS, but could also be used as a standard downcounter. It is based on a 24-bit downcounter with autoreload capability and a programmable clock source. It features a maskable system interrupt generation when the counter reaches '0'.

# 3.14.5 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

# 3.14.6 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

# 3.15 Communication interfaces

# 3.15.1 I<sup>2</sup>C bus

Up to three I<sup>2</sup>C interfaces (I2C1 and I2C3) can operate in multimaster or slave modes.

Each I<sup>2</sup>C interface can support Standard mode (Sm, up to 100 kbit/s), Fast mode (Fm, up to 400 kbit/s) and Fast Mode Plus (Fm+, up to 1 Mbit/s) with 20 mA output drive on some I/Os.

7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask) are also supported as well as programmable analog and digital noise filters.

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks
Benefits	Available in Stop mode	Extra filtering capability vs. standard requirements.     Stable length
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

Table 10. Comparison of I2C analog and digital filters

In addition, I2C1 and I2C3 provide hardware support for SMBus 2.0 and PMBus 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. I2C1/I2C3 also have a clock domain independent from the CPU clock, allowing the I2C1/I2C3 to wake up the MCU from Stop mode on address match.

Each I2C interface can be served by the DMA controller.

Refer to *Table 11* for an overview of I2C interface features.

I2C features<sup>(1)</sup> **I2C1 I2C2 I2C3** Χ Χ 7-bit addressing mode Х Χ Χ Χ 10-bit addressing mode Standard mode (up to 100 kbit/s) Χ Χ Χ Fast mode (up to 400 kbit/s) Χ Χ Χ Fast Mode Plus with 20 mA output drive I/Os (up to 1  $X^{(2)}$ Х Χ Mbit/s) Independent clock Χ Х **SMBus** Χ Χ Wakeup from STOP Χ Х

Table 11. STM32L071xx I<sup>2</sup>C implementation



<sup>1.</sup> X = supported.

See Table 15: STM32L071xxx pin definition on page 39 for the list of I/Os that feature Fast Mode Plus capability

# 3.15.2 Universal synchronous/asynchronous receiver transmitter (USART)

The four USART interfaces (USART1, USART2, USART4 and USART5) are able to communicate at speeds of up to 4 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1 and USART2 also support SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability, auto baud rate feature and has a clock domain independent from the CPU clock, allowing to wake up the MCU from Stop mode using baudrates up to 42 Kbaud.

All USART interfaces can be served by the DMA controller.

*Table 12* for the supported modes and features of USART interfaces.

USART modes/features<sup>(1)</sup> **USART1 and USART2 USART4 and USART5** Hardware flow control for modem Х Χ Χ Continuous communication using DMA Multiprocessor communication Χ Χ Synchronous mode (2) Χ Χ Smartcard mode Х Single-wire half-duplex communication Х Х IrDA SIR ENDEC block Χ Х I IN mode Dual clock domain and wakeup from Stop mode Χ Receiver timeout interrupt Х Х Modbus communication Х Auto baud rate detection (4 modes) Х **Driver Enable** Χ

**Table 12. USART implementation** 

# 3.15.3 Low-power universal asynchronous receiver transmitter (LPUART)

The devices embed one Low-power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock. It can wake up the system from Stop mode using baudrates up to 46 Kbaud. The Wakeup events from Stop mode are programmable and can be:

- Start bit detection
- Or any received data frame
- Or a specific programmed data frame

<sup>1.</sup> X = supported.

<sup>2.</sup> This mode allows using the USART as an SPI master.

Only a 32.768 kHz clock (LSE) is needed to allow LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.

### 3.15.4 Serial peripheral interface (SPI)/Inter-integrated sound (I2S)

Up to two SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The USARTs with synchronous capability can also be used as SPI master.

One standard I2S interfaces (multiplexed with SPI2) is available. It can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When the I2S interfaces is configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The SPIs can be served by the DMA controller.

Refer to *Table 13* for the differences between SPI1 and SPI2.

SPI features <sup>(1)</sup>	SPI1	SPI2
Hardware CRC calculation	Х	Х
I2S mode	-	Х
TI mode	Х	Х

Table 13. SPI/I2S implementation

# 3.16 Cyclic redundancy check (CRC) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

# 3.17 Serial wire debug port (SW-DP)

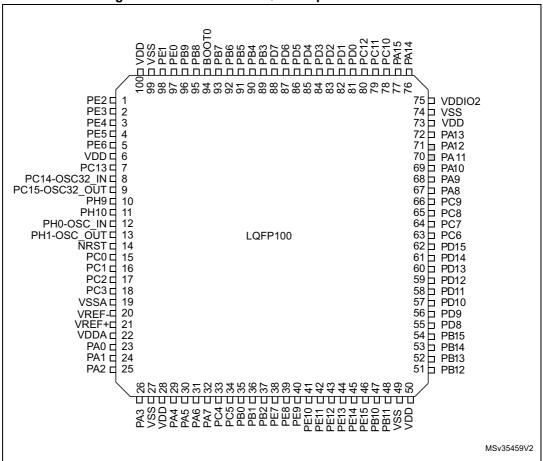
An Arm SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

<sup>1.</sup> X = supported.

STM32L071xx Pin descriptions

# 4 Pin descriptions

Figure 3. STM32L071xx LQFP100 pinout - 14 x 14 mm



- 1. The above figure shows the package top view.
- 2. PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

Pin descriptions STM32L071xx

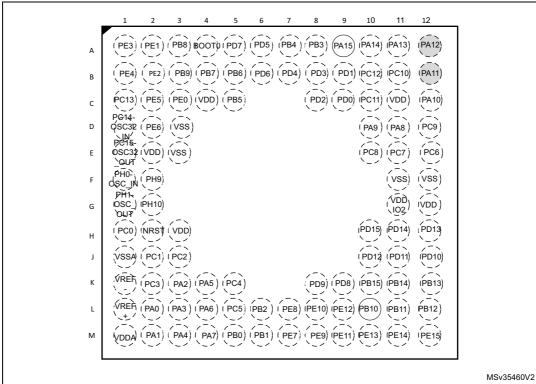


Figure 4. STM32L071xx UFBGA100 ballout - 7x 7 mm

- 1. The above figure shows the package top view.
- 2. PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

VDD VS S PB 9 PB 8 PB 8 PB 7 PB 7 PB 6 PB 7 PB 6 PB 7 PB 6 PD 2 PC11 PC11 PC11 PC11 PC11 PC10 PA 14 PA 15 PA 14 64 63 62 61 60 59 58 57 56 55 54 53 52 51 50 49 48 D VDDIO2  $v_{DD}$ □ 1 47 VSS **口** 2 PC13 PC 14-OSC 32 IN 46 PA 13 PC 15-OSC 32\_OUT 45 PA 12 PHO-OS C\_IN □ 5 44 PA 11 PH1-OSC\_OUT 43 PA 10 □ 6 42 PA 9 NRST 口 7 41 PA 8 PC0 Ц 8 LQFP64 PC1 □ 9 40 PC9 PC2 □ 10 39 □ PC8 PC3 □ 11 38 PC7 VSS A 37 PC6 □ 12 36 □ PB 15 VDD A □ 13 35 PB 14 PA0 □ 14 PA 1 15 34 PB 13 1819 20 21 22 23 24 25 26 27 28 29 30 31 33 PB 12 PA 2 1 16 PA3 VSS VDD PA4 PA5 PA7 PC4 PC4 PC5 PB 1 PB 1 PB 2 PB 1 VSS VDD MSv35457V2

Figure 5. STM32L071xx LQFP64 pinout - 10 x 10 mm

- 1. The above figure shows the package top view.
- 2. PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

STM32L071xx Pin descriptions

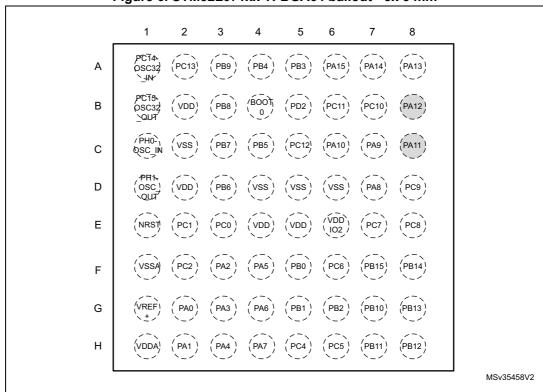


Figure 6. STM32L071xx TFBGA64 ballout - 5x 5 mm

<sup>1.</sup> The above figure shows the package top view.

<sup>2.</sup> PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

Pin descriptions STM32L071xx

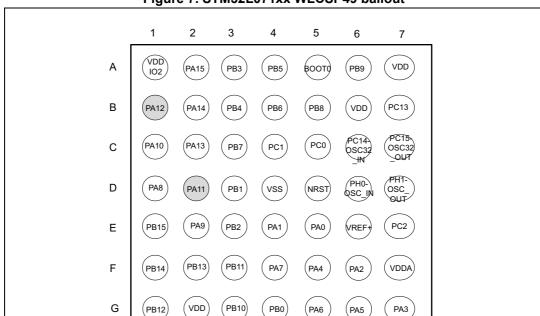


Figure 7. STM32L071xx WLCSP49 ballout

1. The above figure shows the package top view.

2. PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

MSv36157V3

STM32L071xx Pin descriptions

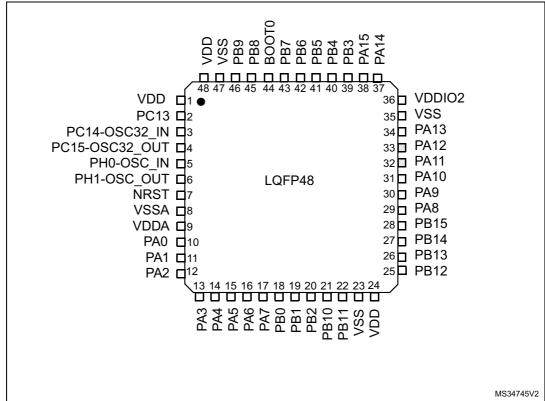


Figure 8. STM32L071xx LQFP48 pinout - 7 x 7 mm

- 1. The above figure shows the package top view.
- 2. PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

VSS BOOT0 PB7 PB6 PB5 PB4 PB3 32 31 30 29 28 27 26 25 24 PA14 VDD 🗆 PC14-OSC32\_IN ☐2 23 PA13 PC15-OSC32\_OUT 3 22 PA12 21 PA11 NRST ☐4 LQFP32 20 PA10 19 PA9 18 PA8 VDDA ☐ 5 PA0 ☐6 PA1 ☐ 7 17 VDD MSv35429V3

Figure 9. STM32L071xx LQFP32 pinout

1. The above figure shows the package top view.

Pin descriptions STM32L071xx

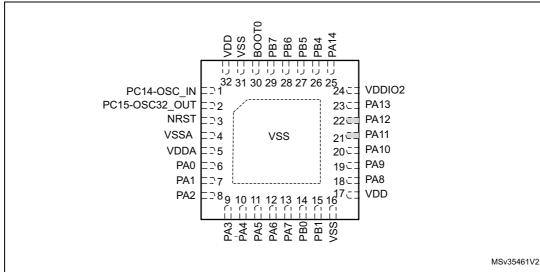


Figure 10. STM32L071xx UFQFPN32 pinout

- 1. The above figure shows the package top view.
- 2. PA11 and PA12 input/output (greyed out pins) are supplied by VDDIO2.

Table 14. Legend/abbreviations used in the pinout table

	IUN	<u> </u>	ations used in the pinout table				
Nar	ne	Abbreviation	Definition				
Pin n	ame	<u> </u>	ed in brackets below the pin name, the pin function during ne as the actual pin name				
		S	Supply pin				
Pin t	уре	I	Input only pin				
		I/O	Input / output pin				
		FT 5 V tolerant I/O					
		FTf	5 V tolerant I/O, FM+ capable				
I/O stru	ucture	TC Standard 3.3V I/O					
		В	Dedicated BOOT0 pin				
		RST	Bidirectional reset pin with embedded weak pull-up resistor				
Not	es	Unless otherwise specific after reset.	ed by a note, all I/Os are set as floating inputs during and				
Pin functions	Alternate functions	Functions selected throu	gh GPIOx_AFR registers				
FITTUTICUOTIS	Additional functions	Functions directly selected	ed/enabled through peripheral registers				

STM32L071xx Pin descriptions

Table 15. STM32L071xxx pin definition

			Pin n	umb	er			DIE 15. 51W32					
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	-	-	-	1	B2	PE2	I/O	FT	-	TIM3_ETR	-
-	-	-	-	-	-	2	A1	PE3	I/O	FT	1	TIM22_CH1, TIM3_CH1	-
-	-	-	-	-	-	3	В1	PE4	I/O	FT	-	TIM22_CH2, TIM3_CH2	-
-	-	-	-	-	-	4	C2	PE5	I/O	FT	-	TIM21_CH1, TIM3_CH3	-
-	-	-	-	-	-	5	D2	PE6	I/O	FT	-	TIM21_CH2, TIM3_CH4	RTC_TAMP3/WKUP3
1	-	1	1	B2	В6	6	E2	VDD	S		-		-
-	-	2	2	A2	В7	7	C1	PC13	I/O	FT	1	-	RTC_TAMP1/ RTC_TS/ RTC_OUT/WKUP2
2	1	3	3	A1	C6	8	D1	PC14- OSC32_IN (PC14)	I/O	FT	-	-	OSC32_IN
3	2	4	4	B1	C7	9	E1	PC15- OSC32_OUT (PC15)	I/O	тс	1	-	OSC32_OUT
-	-	-	-	-	-	10	F2	PH9	I/O	FT	-	-	-
-	-	-	-	-	-	11	G2	PH10	I/O	FT	-	-	-
-	-	5	5	C1	D6	12	F1	PH0-OSC_IN (PH0)	I/O	тс	-	-	OSC_IN
-	-	6	6	D1	D7	13	G1	PH1- OSC_OUT (PH1)	1/0	TC	ı	-	OSC_OUT
4	3	7	7	E1	D5	14	H2	NRST	I/O	-	-	-	-
-	-	-	8	E3	C5	15	H1	PC0	I/O	FTf	1	LPTIM1_IN1, EVENTOUT, LPUART1_RX, I2C3_SCL	ADC_IN10
-	-	-	9	E2	C4	16	J2	PC1	I/O	FTf	1	LPTIM1_OUT, EVENTOUT, LPUART1_TX, I2C3_SDA	ADC_IN11
-	-	-	10	F2	E7	17	J3	PC2	I/O	FTf	-	LPTIM1_IN2, SPI2_MISO/I2S2_MCK	ADC_IN12

Pin descriptions STM32L071xx

Table 15. STM32L071xxx pin definition (continued)

			Pin n	umb	er							ion (continued)	
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	11	-	-	18	K2	PC3	I/O	FT	-	LPTIM1_ETR, SPI2_MOSI/I2S2_SD	ADC_IN13
-	4	8	12	F1	-	19	J1	VSSA	S		ı	-	-
-	-	-	-	-	-	20	K1	VREF-	S		ı	-	-
-	-	-	-	G1	E6	21	L1	VREF+	S		ı	-	-
5	5	တ	13	H1	F7	22	M1	VDDA	S		ı	-	-
6	6	10	14	G2	E5	23	L2	PA0	I/O	ТТа	-	TIM2_CH1, USART2_CTS, TIM2_ETR, USART4_TX, COMP1_OUT	COMP1_INM, ADC_IN0, RTC_TAMP2/WKUP1
7	7	11	15	H2	E4	24	M2	PA1	I/O	FT	1	EVENTOUT, TIM2_CH2, USART2_RTS_DE, TIM21_ETR, USART4_RX	COMP1_INP, ADC_IN1
8	8	12	16	F3	F6	25	K3	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, USART2_TX, LPUART1_TX, COMP2_OUT	COMP2_INM, ADC_IN2
9	9	13	17	G3	G7	26	L3	PA3	I/O	FT	1	TIM21_CH2, TIM2_CH4, USART2_RX, LPUART1_RX	COMP2_INP, ADC_IN3
-	-	-	18	C2	-	27	D3	VSS	S	-	-	-	-
-	-	-	19	D2	-	28	НЗ	VDD	S	-	-	-	-
10	10	14	20	НЗ	F5	29	МЗ	PA4	I/O	TC	ı	SPI1_NSS, USART2_CK, TIM22_ETR	COMP1_INM, COMP2_INM, ADC_IN4
11	11	15	21	F4	G6	30	K4	PA5	I/O	TC	-	SPI1_SCK, TIM2_ETR, TIM2_CH1	COMP1_INM, COMP2_INM, ADC_IN5

STM32L071xx Pin descriptions

Table 15. STM32L071xxx pin definition (continued)

		I	Pin n	umb	er							ion (continued)	
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
12	12	16	22	G4	G5	31	L4	PA6	I/O	FT	1	SPI1_MISO, TIM3_CH1, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
13	13	17	23	H4	F4	32	M4	PA7	I/O	FT	1	SPI1_MOSI, TIM3_CH2, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
-	ı	-	24	H5	-	33	K5	PC4	I/O	FT	-	EVENTOUT, LPUART1_TX	ADC_IN14
-	-	-	25	H6	-	34	L5	PC5	I/O	FT	-	LPUART1_RX	ADC_IN15
14	14	18	26	F5	G4	35	M5	PB0	I/O	FT	ı	EVENTOUT, TIM3_CH3	ADC_IN8, VREF_OUT
15	15	19	27	G5	D3	36	M6	PB1	I/O	FT	i	TIM3_CH4, LPUART1_RTS_DE	ADC_IN9, VREF_OUT
-	ı	20	28	G6	E3	37	L6	PB2	I/O	FT	ı	LPTIM1_OUT, I2C3_SMBA	-
-	ı	ı	-	-	-	38	M7	PE7	I/O	FT	ı	USART5_CK/USART5_ RTS_DE	-
-	ı	1	-	-	-	39	L7	PE8	I/O	FT	ı	USART4_TX	-
-	ı	-	-	-	-	40	M8	PE9	I/O	FT	-	TIM2_CH1, TIM2_ETR, USART4_RX	-
-	ı	-	-	-	-	41	L8	PE10	I/O	FT	-	TIM2_CH2, USART5_TX	-
-	-	-	-	-	-	42	М9	PE11	I/O	FT	ı	TIM2_CH3, USART5_RX	-
-	-	-	-	-	-	43	L9	PE12	I/O	FT	-	TIM2_CH4, SPI1_NSS	-
	1		-	-	-	44	M10	PE13	I/O	FT	ı	SPI1_SCK	-
_	1	-	-	-	-	45	M11	PE14	I/O	FT	-	SPI1_MISO	-
_	-	-	-	-	-	46	M12	PE15	I/O	FT	-	SPI1_MOSI	-

Pin descriptions STM32L071xx

Table 15. STM32L071xxx pin definition (continued)

		I	Pin n	umb	er				•			lon (continued)	
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	1	21	29	G7	G3	47	L10	PB10	I/O	FT	1	TIM2_CH3, LPUART1_TX, SPI2_SCK, I2C2_SCL, LPUART1_RX	-
-	1	22	30	H7	F3	48	L11	PB11	I/O	FT	-	EVENTOUT, TIM2_CH4, LPUART1_RX, I2C2_SDA, LPUART1_TX	-
16	16	23	31	D6	D4	49	F12	VSS	S		ı	-	-
17	17	24	32	E6	G2	50	G12	VDD	S		ı	-	-
-	-	25	33	H8	G1	51	L12	PB12	I/O	FT	-	SPI2_NSS/I2S2_WS, LPUART1_RTS_DE, I2C2_SMBA, EVENTOUT	-
-	1	26	34	G8	F2	52	K12	PB13	I/O	FTf	ı	SPI2_SCK/I2S2_CK, MCO, LPUART1_CTS, I2C2_SCL, TIM21_CH1	-
-	1	27	35	F8	F1	53	K11	PB14	I/O	FTf	-	SPI2_MISO/I2S2_MCK, RTC_OUT, LPUART1_RTS_DE, I2C2_SDA, TIM21_CH2	-
-		28	36	F7	E1	54	K10	PB15	I/O	FT	-	SPI2_MOSI/I2S2_SD, RTC_REFIN	-
-	-	-	-	-	-	55	K9	PD8	I/O	FT	ı	LPUART1_TX	-
-	-	-	_	-	-	56	K8	PD9	I/O	FT	ı	LPUART1_RX	-
-	-	-	-	-	-	57	J12	PD10	I/O	FT	ı		-
-	-	-	-	-	-	58	J11	PD11	I/O	FT	-	LPUART1_CTS	-
_	-	-	-	-	-	59	J10	PD12	I/O	FT	-	LPUART1_RTS_DE	-
_	-	-	-	-	-	60	H12	PD13	I/O	FT	-		-
_	-	-	-	-	-	61	H11	PD14	I/O	FT	-		-
-	-	-	-	-	-	62	H10	PD15	I/O	FT	-		-
-	-	-	37	F6	-	63	E12	PC6	I/O	FT		TIM22_CH1, TIM3_CH1	
-	-	-	38	E7	-	64	E11	PC7	I/O	FT	-	TIM22_CH2, TIM3_CH2	-

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STM32L071xx Pin descriptions

Table 15. STM32L071xxx pin definition (continued)

		ı	Pin n	umb	er							ion (continuea)	
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	39	E8	-	65	E10	PC8	I/O	FT	-	TIM22_ETR, TIM3_CH3	-
-	-	-	40	D8	-	66	D12	PC9	I/O	FTf	-	TIM21_ETR, TIM3_CH4, I2C3_SDA	-
18	18	29	41	D7	D1	67	D11	PA8	I/O	FTf	-	MCO, EVENTOUT, USART1_CK, I2C3_SCL	-
19	19	30	42	C7	E2	68	D10	PA9	I/O	FTf	ı	MCO, USART1_TX, I2C1_SCL, I2C3_SMBA	-
20	20	31	43	C6	C1	69	C12	PA10	I/O	FTf	-	USART1_RX, I2C1_SDA	-
21	21	32	44	C8	D2	70	B12	PA11	I/O	FT	-	SPI1_MISO, EVENTOUT, USART1_CTS, COMP1_OUT	-
22	22	33	45	B8	B1	71	A12	PA12	I/O	FT	-	SPI1_MOSI, EVENTOUT, USART1_RTS_DE, COMP2_OUT	-
23	23	34	46	A8	C2	72	A11	PA13	I/O	FT	-	SWDIO, LPUART1_RX	-
-	-	-	ı	-	-	73	C11	VDD	S		ı	-	-
-	-	35	47	D5	-	74	F11	VSS	S		-	-	-
-	24	36	48	E5	A1	75	G11	VDDIO2	S		-	-	-
24	25	37	49	A7	B2	76	A10	PA14	I/O	FT	-	SWCLK, USART2_TX, LPUART1_TX	-
25	1	38	50	A6	A2	77	A9	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1, USART4_RTS_DE	-
-	-	-	51	В7	-	78	B11	PC10	I/O	FT	-	LPUART1_TX, USART4_TX	-
-	-	-	52	В6	-	79	C10	PC11	I/O	FT	-	LPUART1_RX, USART4_RX	-
-	-	-	53	C5	-	80	B10	PC12	I/O	FT	-	USART5_TX, USART4_CK	-

Pin descriptions STM32L071xx

Table 15. STM32L071xxx pin definition (continued)

			Pin n	umb	er							lon (continued)	
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	-	-	-	81	С9	PD0	I/O	FT	-	TIM21_CH1, SPI2_NSS/I2S2_WS	-
-	-	-	-	-	-	82	В9	PD1	I/O	FT	-	SPI2_SCK/I2S2_CK	-
-	-	-	54	В5	-	83	C8	PD2	I/O	FT	-	LPUART1_RTS_DE, TIM3_ETR, USART5_RX	-
-	-	-	-	-	-	84	В8	PD3	I/O	FT	-	USART2_CTS, SPI2_MISO/I2S2_MCK	-
-	-	-	-	-	-	85	В7	PD4	I/O	FT	-	USART2_RTS_DE, SPI2_MOSI/I2S2_SD	-
-	-	-	-	-	-	86	A6	PD5	I/O	FT	ı	USART2_TX	-
-	-	-	-	-	-	87	В6	PD6	I/O	FT	ı	USART2_RX	-
-	-	-	-	-	-	88	A5	PD7	I/O	FT	i	USART2_CK, TIM21_CH2	-
26	-	39	55	A5	А3	89	A8	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT, USART1_RTS_DE, USART5_TX	COMP2_INM
27	26	40	56	A4	В3	90	A7	PB4	I/O	FTf	1	SPI1_MISO, TIM3_CH1, TIM22_CH1, USART1_CTS, USART5_RX, I2C3_SDA	COMP2_INP
28	27	41	57	C4	A4	91	C5	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM3_CH2/TIM22_CH2, USART1_CK, USART5_CK/USART5_ RTS_DE	COMP2_INP
29	28	42	58	D3	В4	92	B5	PB6	I/O	FTf	ı	USART1_TX, I2C1_SCL, LPTIM1_ETR,	COMP2_INP

STM32L071xx Pin descriptions

Table 15. STM32L071xxx pin definition (continued)

		I	Pin n	umb	er								
LQFP32	UFQFPN32 <sup>(1)</sup>	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
30	29	43	59	C3	C3	93	B4	PB7	I/O	FTf	-	USART1_RX, I2C1_SDA, LPTIM1_IN2, USART4_CTS	COMP2_INP, VREF_PVD_IN
31	30	44	60	B4	A5	94	A4	воото	ı		-	-	-
-	1	45	61	ВЗ	B5	95	A3	PB8	I/O	FTf	-	I2C1_SCL	-
-	ı	46	62	А3	A6	96	В3	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-
-	-	-	-	-	-	97	C3	PE0	I/O	FT	-	EVENTOUT	-
_	-	-	-	-	-	98	A2	PE1	I/O	FT	-	EVENTOUT	-
32	31	47	63	D4	-	99	D3	VSS	S		•	-	-
-	32	48	64	E4	A7	100	C4	VDD	S		•	-	-

<sup>1.</sup> UFQFPN32 pinout differs from other STM32 devices except STM32L07xxx and STM32L8xxx.

Table 16. Alternate functions port A

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
F	Port	SPI1/SPI2/I2S2/U SART1/2/ LPUART1/LPTIM 1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I2 C1/TIM2/21	SPI1/SPI2/I2S2/L PUART1/ USART5/LPTIM1/ TIM2/3/EVENTOU T/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/L PUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
	PA0	-	-	TIM2_CH1		USART2_CTS	TIM2_ETR	USART4_TX	COMP1_OUT
	PA1	EVENTOUT		TIM2_CH2		USART2_RTS_ DE	TIM21_ETR	USART4_RX	-
	PA2	TIM21_CH1		TIM2_CH3		USART2_TX	-	LPUART1_TX	COMP2_OUT
	PA3	TIM21_CH2		TIM2_CH4		USART2_RX	-	LPUART1_RX	-
	PA4	SPI1_NSS	-	-		USART2_CK	TIM22_ETR	-	-
	PA5	SPI1_SCK	-	TIM2_ETR			TIM2_CH1	-	-
	PA6	SPI1_MISO		TIM3_CH1		LPUART1_CTS	TIM22_CH1	EVENTOUT	COMP1_OUT
<	PA7	SPI1_MOSI		TIM3_CH2		-	TIM22_CH2	EVENTOUT	COMP2_OUT
Port A	PA8	MCO			EVENTOUT	USART1_CK	ı	-	I2C3_SCL
	PA9	MCO		-		USART1_TX	-	I2C1_SCL	I2C3_SMBA
	PA10	-		-		USART1_RX	-	I2C1_SDA	-
	PA11	SPI1_MISO	-	EVENTOUT		USART1_CTS	ı	-	COMP1_OUT
	PA12	SPI1_MOSI	-	EVENTOUT		USART1_RTS_ DE	-	-	COMP2_OUT
	PA13	SWDIO	-			-	-	LPUART1_RX	
	PA14	SWCLK	-	-	-	USART2_TX	-	LPUART1_TX	-
	PA15	SPI1_NSS		TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	USART4_RTS_ DE	-





Table 17. Alternate functions port B

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
	Port	SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I 2C1/TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/LPTIM 1/TIM2/3/EVENT OUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
	PB0	EVENTOUT		TIM3_CH3		-	-	-	-
	PB1	-		TIM3_CH4		LPUART1_RTS_DE	-	-	-
	PB2	-	-	LPTIM1_OUT		-	-	-	I2C3_SMBA
	PB3	SPI1_SCK		TIM2_CH2		EVENTOUT	USART1_RTS_DE	USART5_TX	-
	PB4	SPI1_MISO		TIM3_CH1		TIM22_CH1	USART1_CTS	USART5_RX	I2C3_SDA
	PB5	SPI1_MOSI		LPTIM1_IN1	I2C1_SMBA	TIM3_CH2/ TIM22_CH2	USART1_CK	USART5_CK/ USART5_RTS_ DE	-
	PB6	USART1_TX	I2C1_SCL	LPTIM1_ETR		-	-	-	-
	PB7	USART1_RX	I2C1_SDA	LPTIM1_IN2		-	-	USART4_CTS	-
Port B	PB8	-		-		I2C1_SCL	-	-	-
Ğ	PB9	-		EVENTOUT	-	I2C1_SDA	SPI2_NSS/ I2S2_WS	-	-
	PB10	-		TIM2_CH3		LPUART1_TX	SPI2_SCK	I2C2_SCL	LPUART1_RX
	PB11	EVENTOUT		TIM2_CH4		LPUART1_RX	-	I2C2_SDA	LPUART1_TX
	PB12	SPI2_NSS/I2S2_WS		LPUART1_RTS_ DE			I2C2_SMBA	EVENTOUT	-
	PB13	SPI2_SCK/I2S2_CK		MCO		LPUART1_CTS	I2C2_SCL	TIM21_CH1	-
	PB14	SPI2_MISO/ I2S2_MCK		RTC_OUT		LPUART1_RTS_DE	I2C2_SDA	TIM21_CH2	-
	PB15	SPI2_MOSI/ I2S2_SD		RTC_REFIN	-	-	-	-	-

5					Table 18. Alter	nate function	ns port C			
			AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
	ı	Port	SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I2C1/ TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3 /EVENTOUT/SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2 /I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/E VENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
		PC0	LPTIM1_IN1		EVENTOUT				LPUART1_RX	I2C3_SCL
		PC1	LPTIM1_OUT		EVENTOUT				LPUART1_TX	I2C3_SDA
		PC2	LPTIM1_IN2		SPI2_MISO/ I2S2_MCK					
,		PC3	LPTIM1_ETR		SPI2_MOSI/ I2S2_SD					
		PC4	EVENTOUT		LPUART1_TX					
		PC5			LPUART1_RX					
	O	PC6	TIM22_CH1		TIM3_CH1					
)	Port	PC7	TIM22_CH2		TIM3_CH2					
		PC8	TIM22_ETR		TIM3_CH3					
		PC9	TIM21_ETR		TIM3_CH4					I2C3_SDA
		PC10	LPUART1_TX						USART4_TX	
		PC11	LPUART1_RX						USART4_RX	
		PC12			USART5_TX				USART4_CK	
		PC13								
		PC14								
		PC15								



Table 19. Alternate functions port D

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
	Port	SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I2C1/ TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3 /EVENTOUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2 /I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/E VENTOUT	I2C3/LPUART1/ COMP1/2/TIM3
	PD0	TIM21_CH1	SPI2_NSS/I2S2_WS	-	-	-	-	-	-
	PD1	-	SPI2_SCK/I2S2_CK	-	-	-	-	-	-
	PD2	LPUART1_RTS_ DE		TIM3_ETR	1	-	1	USART5_RX	-
	PD3	USART2_CTS		SPI2_MISO/ I2S2_MCK	-	-	-	-	-
	PD4	USART2_RTS_D E	SPI2_MOSI/I2S2_SD	-	-	-	-	-	-
	PD5	USART2_TX	-	-	-	-	-	-	-
	PD6	USART2_RX	-	-	-	-	-	-	-
Port D	PD7	USART2_CK	TIM21_CH2	-	-	-	-	-	-
"	PD8	LPUART1_TX		-	-	-	-	-	-
	PD9	LPUART1_RX		-	-	-	-	-	-
	PD10	-		-	-	-	-	-	-
	PD11	LPUART1_CTS		-	-	-	-	-	-
	PD12	LPUART1_RTS_ DE		-	-	-	-	-	-
	PD13	-		-	-	-	-	-	-
	PD14	-		-	-	-	-	-	-
	PD15			-	-	-	-	-	-

	Table 20. Alternate functions port E								
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
F	Port	SPI1/SPI2/I2S2/ USART1/2/ LPUART1/LPTI M1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/I2C1 /TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3 /EVENTOUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2 /I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/LPUART1/ COMP1/2/TIM3
	PE0	-		EVENTOUT	-	-	-	-	-
	PE1	-		EVENTOUT	-	-	-	-	-
	PE2	-		TIM3_ETR	-	-	-	-	-
	PE3	TIM22_CH1		TIM3_CH1	-	-	-	-	-
	PE4	TIM22_CH2	-	TIM3_CH2	-	-	-	-	-
	PE5	TIM21_CH1	-	TIM3_CH3	-	-	-	-	-
	PE6	TIM21_CH2	-	TIM3_CH4	-	-	-	-	-
Port E	PE7	-		-	-	-	-	USART5_CK/U SART5_RTS_D E	-
	PE8	-		-	-	-	-	USART4_TX	-
	PE9	TIM2_CH1		TIM2_ETR	-	-	-	USART4_RX	-
	PE10	TIM2_CH2		-	-	-	-	USART5_TX	-
	PE11	TIM2_CH3	-	-	-	-	-	USART5_RX	-
	PE12	TIM2_CH4	-	SPI1_NSS	-	-	-	-	-
	PE13	-		SPI1_SCK	-	-	-	-	-
	PE14	-		SPI1_MISO	-	-	-	-	-
	PE15	-		SPI1_MOSI	-	-	-	-	-





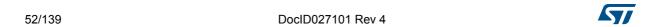
### Table 21. Alternate functions port H

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Port  T PH0		SPI1/SPI2/ I2S2/USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2 /I2C1/TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3/ EVENTOUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/ LPUART1/ COMP1/2/ TIM3
	PH0		-	-	-	-	-	-	-
Port	PH1	-	-	-	-	-	-	-	-

Memory mapping STM32L071xx

# 5 Memory mapping

Refer to the product line reference manual for details on the memory mapping as well as the boundary addresses for all peripherals.



#### 6 Electrical characteristics

#### 6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V<sub>SS</sub>.

#### 6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A = 25$  °C and  $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3 $\sigma$ ).

#### 6.1.2 Typical values

Unless otherwise specified, typical data are based on  $T_A$  = 25 °C,  $V_{DD}$  = 3.6 V (for the 1.65 V  $\leq$ V $_{DD}$   $\leq$ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$ ).

### 6.1.3 Typical curves

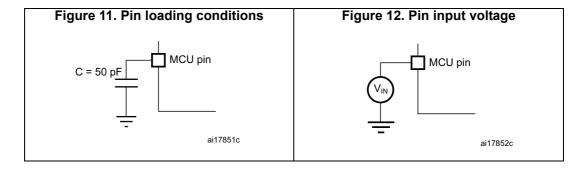
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

#### 6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

#### 6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.



### 6.1.6 Power supply scheme

Standby-power circuitry (OSC32,RTC,Wake-up logic, RTC backup registers) Ю GP I/Os Logic Kernel logic (CPU, Digital & Memories) Regulator N × 100 nF + 1 × 10  $\mu$ F  $V_{\text{DDA}}$  $V_{\text{DDA}}$  $V_{REF+}$ 100 nF Analog: RC,PLL,COMP, + 1 µF ADC  $V_{REF-}$  $V_{SSA}$ MSv34740V1

Figure 13. Power supply scheme

### 6.1.7 Current consumption measurement

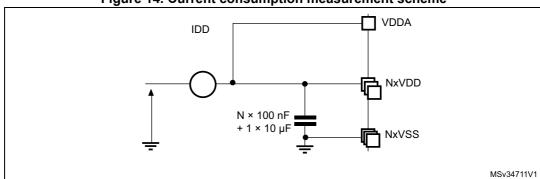


Figure 14. Current consumption measurement scheme

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### 6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 22: Voltage characteristics*, *Table 23: Current characteristics*, and *Table 24: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

	Table 22. Voltage Characteristics						
Symbol	Definition	Min	Max	Unit			
V <sub>DD</sub> -V <sub>SS</sub>	External main supply voltage (including V <sub>DDA</sub> , V <sub>DDIO2</sub> V <sub>DD</sub> ) <sup>(1)</sup>	-0.3	4.0				
V <sub>IN</sub> <sup>(2)</sup>	Input voltage on FT and FTf pins	V <sub>SS</sub> -0.3	V <sub>DD</sub> +4.0	]			
	Input voltage on TC pins	V <sub>SS</sub> -0.3	4.0	V			
VIN.	Input voltage on BOOT0	V <sub>SS</sub>	V <sub>DD</sub> +4.0				
	Input voltage on any other pin	V <sub>SS</sub> -0.3	4.0				
ΔV <sub>DD</sub>	Variations between different V <sub>DDx</sub> power pins	-	50				
V <sub>DDA</sub> -V <sub>DDx</sub>	Variations between any $V_{DDx}$ and $V_{DDA}$ power pins <sup>(3)</sup>	-	300	mV			
ΔV <sub>SS</sub>	Variations between all different ground pins including $V_{REF^-}$ pin	-	50				
V <sub>REF+</sub> –V <sub>DDA</sub>	Allowed voltage difference for V <sub>REF+</sub> > V <sub>DDA</sub>	-	0.4	V			
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	see Section 6.3.11					

Table 22. Voltage characteristics

All main power (V<sub>DD</sub>,, V<sub>DDA</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supply, in the permitted range.

<sup>2.</sup> V<sub>IN</sub> maximum must always be respected. Refer to *Table* 23 for maximum allowed injected current values.

<sup>3.</sup> It is recommended to power  $V_{DD}$  and  $V_{DDA}$  from the same source. A maximum difference of 300 mV between  $V_{DD}$  and  $V_{DDA}$  can be tolerated during power-up and device operation.  $V_{DDIO2}$  is independent from  $V_{DD}$  and  $V_{DDA}$ : its value does not need to respect this rule.

**Table 23. Current characteristics** 

Symbol	Ratings	Max.	Unit
$\Sigma I_{VDD}^{(2)}$	Total current into sum of all V <sub>DD</sub> power lines (source) <sup>(1)</sup>	105	
ΣI <sub>VSS</sub> <sup>(2)</sup>	Total current out of sum of all V <sub>SS</sub> ground lines (sink) <sup>(1)</sup>	105	
ΣI <sub>VDDIO2</sub>	Total current into V <sub>DDIO2</sub> power line (source)	25	
I <sub>VDD(PIN)</sub>	Maximum current into each V <sub>DD</sub> power pin (source) <sup>(1)</sup>	100	
I <sub>VSS(PIN)</sub>	Maximum current out of each V <sub>SS</sub> ground pin (sink) <sup>(1)</sup>	100	
	Output current sunk by any I/O and control pin except FTf pins	16	
I <sub>IO</sub>	Output current sunk by FTf pins	22	
	Output current sourced by any I/O and control pin	-16	mA
	Total output current sunk by sum of all IOs and control pins except PA11 and PA12 <sup>(2)</sup>	90	
ΣΙ <sub>ΙΟ(PIN)</sub>	Total output current sunk by PA11 and PA12	25	
	Total output current sourced by sum of all IOs and control pins <sup>(2)</sup>	-90	
1	Injected current on FT, FTf, RST and B pins	-5/+0 <sup>(3)</sup>	
I <sub>INJ(PIN)</sub>	Injected current on TC pin	± 5 <sup>(4)</sup>	
ΣΙ <sub>ΙΝJ(PIN)</sub>	Total injected current (sum of all I/O and control pins) <sup>(5)</sup>	± 25	

- All main power (V<sub>DD</sub>, V<sub>DDA</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supply, in the permitted range.
- This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
- Positive current injection is not possible on these I/Os. A negative injection is induced by V<sub>IN</sub><V<sub>SS</sub>. I<sub>INJ(PIN)</sub> must never be exceeded. Refer to *Table 22* for maximum allowed input voltage values.
- A positive injection is induced by V<sub>IN</sub> > V<sub>DD</sub> while a negative injection is induced by V<sub>IN</sub> < V<sub>SS</sub>. I<sub>INJ(PIN)</sub> must never be exceeded. Refer to *Table 22: Voltage characteristics* for the maximum allowed input voltage values.
- When several inputs are submitted to a current injection, the maximum ΣI<sub>INJ(PIN)</sub> is the absolute sum of the
  positive and negative injected currents (instantaneous values).

**Table 24. Thermal characteristics** 

Symbol	Ratings	Value	Unit
T <sub>STG</sub>	Storage temperature range	-65 to +150	°C
T <sub>J</sub>	Maximum junction temperature	150	°C

## 6.3 Operating conditions

### 6.3.1 General operating conditions

Table 25. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit		
$f_{HCLK}$	Internal AHB clock frequency	-	0	32			
f <sub>PCLK1</sub>	Internal APB1 clock frequency	-	0	32	MHz		
f <sub>PCLK2</sub>	Internal APB2 clock frequency	-	0	32			
		BOR detector disabled	1.65	3.6			
$V_{DD}$	Standard operating voltage	BOR detector enabled, at power-on	1.8	3.6	V		
		BOR detector disabled, after power-on	1.65	3.6			
$V_{DDA}$	Analog operating voltage (all features)	Must be the same voltage as V <sub>DD</sub> <sup>(1)</sup>	1.65	3.6	٧		
V <sub>DDIO2</sub>	Standard operating voltage	-	1.65	3.6	V		
	Input voltage on FT, FTf and RST	2.0 V ≤V <sub>DD</sub> ≤3.6 V	-0.3	5.5			
V	pins <sup>(2)</sup>	1.65 V ≤V <sub>DD</sub> ≤2.0 V	-0.3	5.2	] ,,		
V <sub>IN</sub>	Input voltage on BOOT0 pin	-	0	5.5	V		
	Input voltage on TC pin	-	-0.3	V <sub>DD</sub> +0.3	1		
		UFBGA100 package	-	351			
	Power dissipation at $T_A = 85 ^{\circ}\text{C}$ (range 6) or $T_A = 105 ^{\circ}\text{C}$ (rage 7) (3)	LQFP100 package	-	488			
		TFBGA64 package	-	313	- -		
		LQFP64 package	-	435			
		WLCSP49 package	-	417			
		LQFP48 package	-	370			
		UFQFPN32 package	-	556			
D		LQFP32 package	-	333	mW		
$P_{D}$		UFBGA100 package	-	88	11100		
		LQFP100 package	-	122			
		TFBGA64 package	-	78			
	Power dissipation at T <sub>A</sub> = 125 °C	LQFP64 package	-	109			
	(range 3) (3)	WLCSP49 package	-	104	1		
		LQFP48 package	-	93			
		UFQFPN32 package	-	139	1		
		LQFP32 package	-	83			

Table 25. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
		Maximum power dissipation (range 6)	-40	85	
TA	Temperature range	Maximum power dissipation (range 7)	-40	105	
		Maximum power dissipation (range 3)	-40	125	°C
	Junction temperature range (range 6)	-40 °C ≤T <sub>A</sub> ≤85 °	-40	105	
TJ	Junction temperature range (range 7)	-40 °C ≤T <sub>A</sub> ≤105 °C	-40	125	
	Junction temperature range (range 3)	-40 °C ≤T <sub>A</sub> ≤125 °C	-40	130	

<sup>1.</sup> It is recommended to power  $V_{DD}$  and  $V_{DDA}$  from the same source. A maximum difference of 300 mV between  $V_{DD}$  and  $V_{DDA}$  can be tolerated during power-up and normal operation.



<sup>2.</sup> To sustain a voltage higher than  $V_{DD}$ +0.3V, the internal pull-up/pull-down resistors must be disabled.

<sup>3.</sup> If  $T_A$  is lower, higher  $P_D$  values are allowed as long as  $T_J$  does not exceed  $T_J$  max (see *Table 24: Thermal characteristics on page 56*).

### 6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the ambient temperature condition summarized in *Table 25*.

Table 26. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
	V sia a tima a mata	BOR detector enabled	0	-	∞			
<b>4</b> (1)	V <sub>DD</sub> rise time rate	BOR detector disabled	0	-	1000	μs/V		
t <sub>VDD</sub> <sup>(1)</sup>	\/ fall time rate	BOR detector enabled	20	-	∞	μs/v		
	V <sub>DD</sub> fall time rate	BOR detector disabled	0	-	1000			
т (1)	Deast temperization	V <sub>DD</sub> rising, BOR enabled	-	2	3.3	ms		
T <sub>RSTTEMPO</sub> <sup>(1)</sup>	Reset temporization	V <sub>DD</sub> rising, BOR disabled <sup>(2)</sup>	0.4	0.7	1.6	ms		
V	Power-on/power down reset	Falling edge	1	1.5	1.65			
V <sub>POR/PDR</sub>	threshold	Rising edge	1.3	1.5	1.65			
	Danis and an add through ald O	Falling edge	1.67	1.7	1.74			
$V_{BOR0}$	Brown-out reset threshold 0	Rising edge	1.69	1.76	1.8			
V <sub>BOR1</sub>	Danis and an act through all d	Falling edge	1.87	1.93	1.97			
	Brown-out reset threshold 1	Rising edge	1.96	2.03	2.07			
V <sub>BOR2</sub>	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35			
		Rising edge	2.31	2.41	2.44			
M	Drawn aut roast throabald 2	Falling edge	2.45	2.55	2.6			
$V_{BOR3}$	Brown-out reset threshold 3	Rising edge	2.54	2.66	2.7			
M	Don to the second the second of the	Falling edge	2.68	2.8	2.85			
$V_{BOR4}$	Brown-out reset threshold 4	Rising edge	2.78	2.9	2.95			
M	Programmable voltage detector	Falling edge	1.8	1.85	1.88	V		
V <sub>PVD0</sub>	threshold 0	Rising edge	1.88	1.94	1.99			
M	DVD throubold 1	Falling edge	1.98	2.04	2.09			
V <sub>PVD1</sub>	PVD threshold 1	Rising edge	2.08	2.14	2.18			
1/	DVD throughold 0	Falling edge	2.20	2.24	2.28			
$V_{PVD2}$	PVD threshold 2	Rising edge	2.28	2.34	2.38			
M	DVD throughold 2	Falling edge	2.39	2.44	2.48			
$V_{PVD3}$	PVD threshold 3	Rising edge	2.47	2.54	2.58			
W	DVD throshold 4	Falling edge	2.57	2.64	2.69			
$V_{PVD4}$	PVD threshold 4	Rising edge	2.68	2.74	2.79			
\/	DVD throubold F	Falling edge	2.77	2.83	2.88			
$V_{PVD5}$	PVD threshold 5	Rising edge	2.87	2.94	2.99			

1440 - 20								
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
\ /	PVD threshold 6	Falling edge	2.97	3.05	3.09	V		
$V_{PVD6}$		Rising edge	3.08	3.15	3.20			
$V_{hyst}$	Hysteresis voltage	BOR0 threshold	-	40	-			
		All BOR and PVD thresholds excepting BOR0	-	100	-	mV		

Table 26. Embedded reset and power control block characteristics (continued)

### 6.3.3 Embedded internal reference voltage

The parameters given in *Table 28* are based on characterization results, unless otherwise specified.

Table 27. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V <sub>DDA</sub> = 3 V	0x1FF8 0078 - 0x1FF8 0079

Table 28. Embedded internal reference voltage<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>REFINT out</sub> <sup>(2)</sup>	Internal reference voltage	– 40 °C < T <sub>J</sub> < +125 °C	1.202	1.224	1.242	V
T <sub>VREFINT</sub>	Internal reference startup time	-	-	2	3	ms
V <sub>VREF_MEAS</sub>	V <sub>DDA</sub> and V <sub>REF+</sub> voltage during V <sub>REFINT</sub> factory measure	-	2.99	3	3.01	V
A <sub>VREF_MEAS</sub>	Accuracy of factory-measured V <sub>REFINT</sub> value <sup>(3)</sup>	Including uncertainties due to ADC and $V_{DDA}/V_{REF+}$ values	1	-	±5	mV
T <sub>Coeff</sub> <sup>(4)</sup>	Temperature coefficient	-40 °C < T <sub>J</sub> < +125 °C	-	25	100	ppm/°C
A <sub>Coeff</sub> <sup>(4)</sup>	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
V <sub>DDCoeff</sub> <sup>(4)</sup>	Voltage coefficient	3.0 V < V <sub>DDA</sub> < 3.6 V	-	-	2000	ppm/V
T <sub>S_vrefint</sub> (4)(5)	ADC sampling time when reading the internal reference voltage	-	5	10	-	μs
T <sub>ADC_BUF</sub> <sup>(4)</sup>	Startup time of reference voltage buffer for ADC	-	-	-	10	μs
I <sub>BUF_ADC</sub> <sup>(4)</sup>	Consumption of reference voltage buffer for ADC	-	-	13.5	25	μA
I <sub>VREF_OUT</sub> <sup>(4)</sup>	VREF_OUT output current <sup>(6)</sup>	-	-	-	1	μΑ
C <sub>VREF_OUT</sub> <sup>(4)</sup>	VREF_OUT output load	-	-	-	50	pF

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<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>LPBUF</sub> <sup>(4)</sup>	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V <sub>REFINT_DIV1</sub> <sup>(4)</sup>	1/4 reference voltage	-	24	25	26	
V <sub>REFINT_DIV2</sub> <sup>(4)</sup>	1/2 reference voltage	-	49	50	51	% V <sub>REFINT</sub>
V <sub>REFINT_DIV3</sub> <sup>(4)</sup>	3/4 reference voltage	-	74	75	76	INCI IINI

Table 28. Embedded internal reference voltage<sup>(1)</sup> (continued)

- Refer to Table 40: Peripheral current consumption in Stop and Standby mode for the value of the internal reference current consumption (I<sub>REFINT</sub>).
- 2. Guaranteed by test in production.
- 3. The internal V<sub>REF</sub> value is individually measured in production and stored in dedicated EEPROM bytes.
- 4. Guaranteed by design.
- 5. Shortest sampling time can be determined in the application by multiple iterations.
- 6. To guarantee less than 1% VREF\_OUT deviation.

#### 6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 14: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code if not specified otherwise.

The current consumption values are derived from the tests performed under ambient temperature and V<sub>DD</sub> supply voltage conditions summarized in *Table 25: General operating conditions* unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time and prefetch is adjusted depending on fHCLK frequency and voltage range to provide the best CPU performance unless otherwise specified.
- When the peripherals are enabled f<sub>APB1</sub> = f<sub>APB2</sub> = f<sub>APB</sub>
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used)
- The HSE user clock applied to OSCI\_IN input follows the characteristic specified in Table 42: High-speed external user clock characteristics
- For maximum current consumption V<sub>DD</sub> = V<sub>DDA</sub> = 3.6 V is applied to all supply pins
- For typical current consumption V<sub>DD</sub> = V<sub>DDA</sub> = 3.0 V is applied to all supply pins if not specified otherwise

The parameters given in *Table 49*, *Table 25* and *Table 26* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 25*.



Table 29. Current consumption in Run mode, code with data processing running from Flash memory

Symbol	Parameter	Conditio	on	f <sub>HCLK</sub> (MHz)	Тур	Max <sup>(1)</sup>	Unit
			Range3,	1	190	250	
			Vcore=1.2 V	2	345	380	μΑ
			VOS[1:0]=11	4	650	670	
		f <sub>HSE</sub> = f <sub>HCLK</sub> up to	Range2,	4	0,8	0,86	
		16MHz included, f <sub>HSE</sub> = f <sub>HCLK</sub> /2 above	Vcore=1.5 V	8	1,55	1,7	
		16 MHz (PLL ON) <sup>(2)</sup>	VOS[1:0]=10	16	2,95	3,1	mA
			Range1, Vcore=1.8 V VOS[1:0]=01	8	1,9	2,1	
I <sub>DD</sub> (Run	Supply current in Run			16	3,55	3,8	
from Flash memory)	mode code executed from Flash memory			32	6,65	7,2	
inemory)	nominasii memory		Range3,	0,065	39	130	
		MSI clock source	Vcore=1.2 V	0,524	115	210	μA
			VOS[1:0]=11	4,2	700	770	
		HSI clock source	Range2, Vcore=1.5 V VOS[1:0]=10	16	2,9	3,2	- mA
		(16MHz)	Range1, Vcore=1.8 V VOS[1:0]=01	32	7,15	7,4	IIIA

<sup>1.</sup> Guaranteed by characterization results at 125  $^{\circ}\text{C},$  unless otherwise specified.

<sup>2.</sup> Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).

**Symbol Conditions** Unit **Parameter** Тур **f**HCLK Dhrystone 650 CoreMark 655 Range 3, Fibonacci 485 V<sub>CORE</sub>=1.2 V, VOS[1:0]=11 4 MHz μΑ while(1) 385 Supply  $I_{DD}$ current in while(1), 1WS,  $f_{HSE}$  =  $f_{HCLK}$  up to 16 MHz included,  $f_{HSE}$ 375 (Run Run mode, prefetch OFF from code =  $f_{HCLK}/2$  above 16 MHz (PLL ON)<sup>(1)</sup> Dhrystone 6,65 Flash executed memory) from Flash CoreMark 6.9 memory Range 1, Fibonacci 6,75 V<sub>CORE</sub>=1.8 V, VOS[1:0]=01 32 MHz mΑ while(1) 5,8 while(1), prefetch 5,5 OFF

Table 30. Current consumption in Run mode vs code type, code with data processing running from Flash memory

<sup>1.</sup> Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).

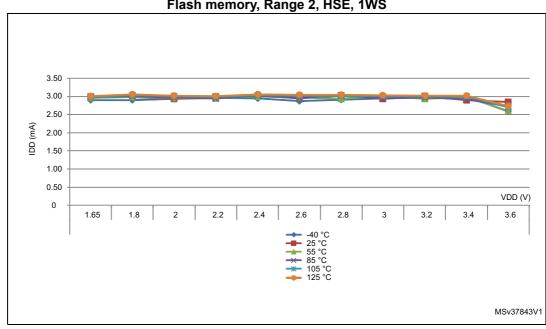


Figure 15.  $I_{DD}$  vs  $V_{DD}$ , at  $T_A$ = 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS

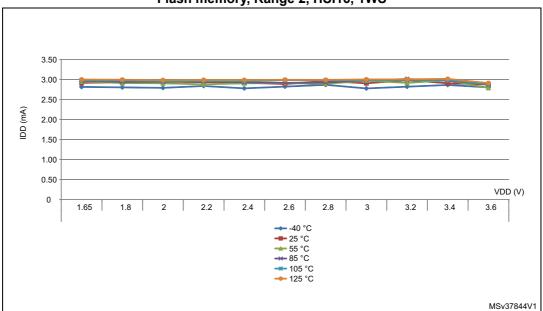


Figure 16.  $I_{DD}$  vs  $V_{DD}$ , at  $T_A$ = 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS

Table 31. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditio	f <sub>HCLK</sub> (MHz)	Тур	Max <sup>(1)</sup>	Unit	
			Range3,	1	175	230	
			Vcore=1.2 V	2	315	360	μΑ
			VOS[1:0]=11	4	570	630	
		$f_{HSE} = f_{HCLK}$ up to	Range2,	4	0,71	0,78	
		16 MHz included, f <sub>HSE</sub> = f <sub>HCLK</sub> /2 above	Vcore=1.5 V	8	1,35	1,6	
		16 MHz (PLL ON) <sup>(2)</sup>	VOS[1:0]=10	16	2,7	3	mA
			Range1,	8	1,7	1,9	IIIA
I <sub>DD</sub> (Run	Supply current in Run mode code executed		Vcore=1.8 V	16	3,2	3,7	
from RAM)	from RAM, Flash		VOS[1:0]=01	32	6,65	7,1	
	memory switched off		Range3,	0,065	38	98	
		MSI clock	Vcore=1.2 V	0,524	105	160	μΑ
			VOS[1:0]=11	4,2	615	710	
		HSI clock source	Range2, Vcore=1.5 V VOS[1:0]=10	16	2,85	3	mΛ
		(16 MHz)	Range1, Vcore=1.8 V VOS[1:0]=01	32	6,85	7,3	mA

<sup>1.</sup> Guaranteed by characterization results at 125 °C, unless otherwise specified.

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2. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).

Table 32. Current consumption in Run mode vs code type, code with data processing running from RAM<sup>(1)</sup>

Symbol	Parameter		Conditions			Тур	Unit
Supply current in			Dhrystone		570		
			Range 3,	CoreMark	4 MHz	670	
		£ _£	V <sub>CORE</sub> =1.2 V, VOS[1:0]=11	Fibonacci	4 IVITZ	410	μΑ
I <sub>DD</sub> (Run from	Run mode, code executed from	f <sub>HSE</sub> = f <sub>HCLK</sub> up to 16 MHz included,		while(1)		375	
RAM)	RAM, Flash memory switched	f <sub>HSE</sub> = f <sub>HCLK</sub> /2 above 16 MHz (PLL ON) <sup>(2)</sup>		Dhrystone		6,65	
	off	10 MHZ (FLL ON)	Range 1, V <sub>CORE</sub> =1.8 V,	CoreMark	32 MHz	6,95	m Λ
			V <sub>CORE</sub> =1.6 V, VOS[1:0]=01	Fibonacci	3∠ IVI⊓∠	5,9	mA
				while(1)		5,2	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.

<sup>2.</sup> Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).

Table 33. Current consumption in Sleep mode

Symbol	Parameter	Condition		f <sub>HCLK</sub> (MHz)	Тур	Max <sup>(1)</sup>	Unit
			Range3,	1	43,5	110	
			Vcore=1.2 V	2	72	110 140 200 220 380 690 460 840 2000 93 110 230 850 2100 130 160 220 240 400 710 470 860 2000 110 120 240	
			VOS[1:0]=11	4	130	200	
		f <sub>HSE</sub> = f <sub>HCLK</sub> up to	Range2,	4	160	220	
		16 MHz included, $f_{HSE} = f_{HCLK}/2$ above	Vcore=1.5 V	8	305	380	
		16 MHz (PLL ON) <sup>(2)</sup>	VOS[1:0]=10	16	590	690	
			Range1,	8	370	460	
	Supply current in Sleep mode, Flash		Vcore=1.8 V	16	715	840	
	memory switched		VOS[1:0]=01	32	1650	2000	
	OFF		Range3,	0,065	18	93	
		MSI clock	Vcore=1.2 V	0,524	31,5	110	
			VOS[1:0]=11	4,2	140	230	
		HSI clock source	Range2, Vcore=1.5 V VOS[1:0]=10	16	665	850	
I <sub>DD</sub>		(16 MHz)	Range1, Vcore=1.8 V VOS[1:0]=01	32	1750	2100	4
(Sleep)			Range3,	1	57,5	130	μA
			Vcore=1.2 V	2	84	160	
			VOS[1:0]=11	4	150	220	
		f <sub>HSE</sub> = f <sub>HCLK</sub> up to	Range2,	4	170	240	
		16MHz included, $f_{HSE} = f_{HCLK}/2$ above	Vcore=1.5 V	8	315	400	
		16 MHz (PLL ON) <sup>(2)</sup>	VOS[1:0]=10	16	605	710	
			Range1,	8	380	470	
	Supply current in Sleep mode, Flash		Vcore=1.8 V	16	730	860	
	memory switched		VOS[1:0]=01	32	1650	2000	
	ON		Range3,	0,065	29,5	110	
		MSI clock	Vcore=1.2 V	0,524	44,5	120	
			VOS[1:0]=11	4,2	150	240	
		HSI clock source	Range2, Vcore=1.5 V VOS[1:0]=10	16	680	930	
		(16MHz)	Range1, Vcore=1.8 V VOS[1:0]=01	32	1750	2200	

<sup>1.</sup> Guaranteed by characterization results at 125  $^{\circ}\text{C},$  unless otherwise specified.

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2. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).

Table 34. Current consumption in Low-power run mode

Symbol	Parameter		Condition					Unit	
				$T_A = -40 \text{ to } 25^{\circ}\text{C}$		9,45	12		
			MSI clock = 65 kHz,	T <sub>A</sub> = 85°C	0,032	14	58		
			f <sub>HCLK</sub> = 32 kHz	T <sub>A</sub> = 105°C	0,032	21	64		
				T <sub>A</sub> = 125°C		36,5	160		
		All peripherals		$T_A = -40 \text{ to } 25^{\circ}\text{C}$		14,5	18	μA	
		OFF, code executed from	MSI clock = 65 kHz,	T <sub>A</sub> = 85°C	0,065	19,5	60		
Supply		RAM, Flash	f <sub>HCLK</sub> = 65kHz	T <sub>A</sub> = 105°C	0,005	26	65		
		memory switched OFF, V <sub>DD</sub> from		T <sub>A</sub> = 125°C		42	160		
	1.65 to 3.6 V		$T_A = -40 \text{ to } 25^{\circ}\text{C}$		26,5	30			
			MOL ala ala 404 lalla	T <sub>A</sub> = 55°C		27,5	60		
			MSI clock=131 kHz, f <sub>HCLK</sub> = 131 kHz	T <sub>A</sub> = 85°C	0,131	31	66		
	Supply		HOLK	T <sub>A</sub> = 105°C		37,5	77		
I <sub>DD</sub>	current in			T <sub>A</sub> = 125°C		53,5	170	пΔ	
(LP Run)	Low-power run mode			$T_A = -40 \text{ to } 25^{\circ}\text{C}$	0,032	24,5	34	170 µA	
	Turi mode		MSI clock = 65 kHz, f <sub>HCLK</sub> = 32 kHz	T <sub>A</sub> = 85°C		30	82		
				T <sub>A</sub> = 105°C		38,5	90		
				T <sub>A</sub> = 125°C		58	120		
		All peripherals		$T_A = -40 \text{ to } 25^{\circ}\text{C}$		30,5	40		
		OFF, code	MSI clock = 65 kHz,	T <sub>A</sub> = 85°C	0,065	36,5	88		
		executed from Flash memory,	f <sub>HCLK</sub> = 65 kHz	T <sub>A</sub> = 105°C	0,003	45	96		
		VDD from 1.65 V		T <sub>A</sub> = 125°C		64,5	120		
		to 3.6 V		$T_A = -40 \text{ to } 25^{\circ}\text{C}$		45	56		
			MSI clock =	T <sub>A</sub> = 55°C	0,131	48	96		
			131 kHz,	T <sub>A</sub> = 85°C		51	110		
			f <sub>HCLK</sub> = 131 kHz	T <sub>A</sub> = 105°C		59,5	120		
				T <sub>A</sub> = 125°C		79,5	150		

<sup>1.</sup> Guaranteed by characterization results at 125 °C, unless otherwise specified.

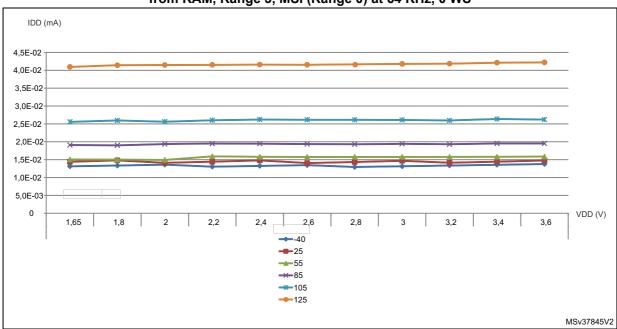


Figure 17.  $I_{DD}$  vs  $V_{DD}$ , at  $T_A$ = 25 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

Table 35. Current consumption in Low-power sleep mode

Symbol	Parameter		Condition				
			MSI clock = 65 kHz, f <sub>HCLK</sub> = 32 kHz, Flash memory OFF	$T_A = -40 \text{ to } 25^{\circ}\text{C}$	4,7	-	
				$T_A = -40 \text{ to } 25^{\circ}\text{C}$	17	24	
			MSI clock = 65 kHz,	T <sub>A</sub> = 85°C	19,5	30	
			f <sub>HCLK</sub> = 32 kHz	T <sub>A</sub> = 105°C	23	47	
		All marinhanala		T <sub>A</sub> = 125°C	32,5	70	
	Supply current in	All peripherals OFF, code		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	17	24	
(LP Sleep)	Low-power sleep mode	executed from Flash memory, V <sub>DD</sub>	MSI clock = 65 kHz,	T <sub>A</sub> = 85°C	20	31	μA
	mode	from 1.65 to 3.6 V	f <sub>HCLK</sub> = 65 kHz	T <sub>A</sub> = 105°C	23,5	47	
				T <sub>A</sub> = 125°C	32,5	70	
				$T_A = -40 \text{ to } 25^{\circ}\text{C}$	19,5	27	
				T <sub>A</sub> = 55°C	20,5	28	
			MSI clock = 131kHz, f <sub>HCLK</sub> = 131 kHz	T <sub>A</sub> = 85°C	22,5	33	
			HOLK	T <sub>A</sub> = 105°C	26	50	
				T <sub>A</sub> = 125°C	35	73	

<sup>1.</sup> Guaranteed by characterization results at 125  $^{\circ}\text{C},$  unless otherwise specified.

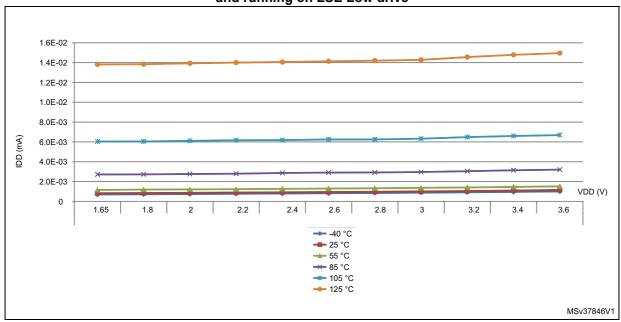
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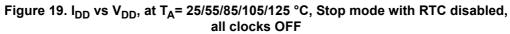
Table 36. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Тур	Max <sup>(1)</sup>	Unit
		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	0,43	1,00	
		T <sub>A</sub> = 55°C	0,735	2,50	
I <sub>DD</sub> (Stop)	Supply current in Stop mode	T <sub>A</sub> = 85°C	2,25	4,90	μA
		T <sub>A</sub> = 105°C	5,3	13,00	
		T <sub>A</sub> = 125°C	12,5	28,00	

<sup>1.</sup> Guaranteed by characterization results at 125 °C, unless otherwise specified.

Figure 18.  $I_{DD}$  vs  $V_{DD}$ , at  $T_A$ = 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive





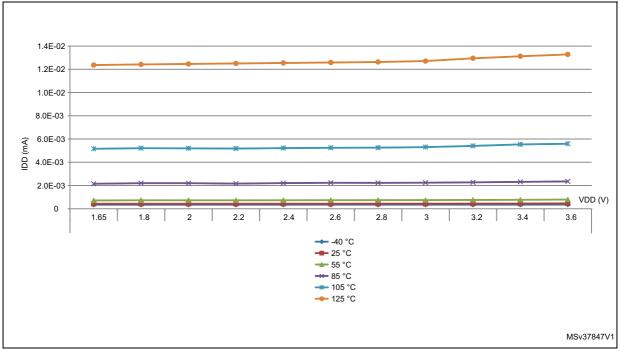


Table 37. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditi	ons	Тур	Max <sup>(1)</sup>	Unit
			$T_A = -40 \text{ to } 25^{\circ}\text{C}$	0,855	1,70	
			T <sub>A</sub> = 55 °C	-	2,90	
		Independent watchdog and LSI enabled	T <sub>A</sub> = 85 °C	-	3,30	
		and Lor chabicu	T <sub>A</sub> = 105 °C	-	4,10	
I <sub>DD</sub>	Supply current in Standby		T <sub>A</sub> = 125 °C	-	8,50	]
(Standby)	mode		$T_A = -40 \text{ to } 25^{\circ}\text{C}$	0,29	0,60	- μA
			T <sub>A</sub> = 55 °C	0,32	1,20	
		Independent watchdog and LSI OFF	T <sub>A</sub> = 85 °C	0,5	2,30	
		aa 20. 0	T <sub>A</sub> = 105 °C	0,94	3,00	
			T <sub>A</sub> = 125 °C	2,6	7,00	

<sup>1.</sup> Guaranteed by characterization results at 125 °C, unless otherwise specified

Table 38. Average current consumption during Wakeup

Symbol	Symbol parameter		Current consumption during wakeup	Unit	
		HSI	1		
		HSI/4	0,7		
I <sub>DD</sub> (Wakeup from Stop)	Supply current during Wakeup from Stop mode	MSI clock = 4,2 MHz	0,7		
2.547	out we was	MSI clock = 1,05 MHz	0,4		
		MSI clock = 65 KHz	0,1	mA	
I <sub>DD</sub> (Reset)	Reset pin pulled down	-	0,21	110.	
I <sub>DD</sub> (Power-up)	BOR ON	-	0,23		
I <sub>DD</sub> (Wakeup from	With Fast wakeup set	MSI clock = 2,1 MHz	0,5		
StandBy)	With Fast wakeup disabled	MSI clock = 2,1 MHz	0,12		

#### On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- $\bullet$   $\,$  all I/O pins are in input mode with a static value at  $V_{DD}$  or  $V_{SS}$  (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked OFF
  - with only one peripheral clocked on

Table 39. Peripheral current consumption in Run or Sleep mode<sup>(1)</sup>

		Typical	consumption, V	/ <sub>DD</sub> = 3.0 V, T <sub>A</sub> =	25 °C	
Per	ripheral	Range 1, V <sub>CORE</sub> =1.8 V VOS[1:0] = 01	Range 2, V <sub>CORE</sub> =1.5 V VOS[1:0] = 10	Range 3, V <sub>CORE</sub> =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit
	CRS	2.5	2	2	2	
	I2C1	11	9.5	7.5	9	
	I2C3	11	9	7	9	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	
	SPI2	9	4.5	3.5	4	
APB1	USART2	14.5	12	9.5	11	μΑ/MHz
APDI	USART4	5	4	3	5	(f <sub>HCLK</sub> )
	USART5	5	4	3	5	
	TIM2	10.5	8.5	7	9	
	TIM3	12	10	8	11	
	TIM6	3.5	3	2.5	2	
	TIM7	3.5	3	2.5	2	
	WWDG	3	2	2	2	
	ADC1 <sup>(2)</sup>	5.5	5	3.5	4	
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
4 DD0	TIM21	7.5	6	5	5.5	μΑ/MHz
APB2	TIM22	7	6	5	6	(f <sub>HCLK</sub> )
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	



Table 39. Peripheral current consumption in Run or Sleep mode<sup>(1)</sup> (continued)

		Typical	consumption, V	/ <sub>DD</sub> = 3.0 V, T <sub>A</sub> =	25 °C	
Per	ipheral		Range 2, V <sub>CORE</sub> =1.5 V VOS[1:0] = 10		Low-power sleep and run	Unit
	GPIOA	3.5	3	2.5	2.5	
	GPIOB	3.5	2.5	2	2.5	
Cortex- M0+ core	GPIOC	8.5	6.5	5.5	7	μΑ/MHz
I/O port	GPIOD	1	0.5	0.5	0.5	(f <sub>HCLK</sub> )
	GPIOE	8	6	5	6	
	GPIOH	1.5	1	1	0.5	
	CRC	1.5	1	1	1	
AHB	FLASH	0(3)	0(3)	0(3)	0(3)	μΑ/MHz (f <sub>HCLK</sub> )
	DMA1	10	8	6.5	8.5	('HCLK)
All e	enabled	204	162	130	202	μΑ/ΜΗz (f <sub>HCLK</sub> )
F	PWR	2.5	2	2	1	μΑ/ΜΗz (f <sub>HCLK</sub> )

Data based on differential I<sub>DD</sub> measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f<sub>HCLK</sub> = 32 MHz (range 1), f<sub>HCLK</sub> = 16 MHz (range 2), f<sub>HCLK</sub> = 4 MHz (range 3), f<sub>HCLK</sub> = 64kHz (Low-power run/sleep), f<sub>APB1</sub> = f<sub>HCLK</sub>, f<sub>APB2</sub> = f<sub>HCLK</sub>, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.

<sup>2.</sup> HSI oscillator is OFF for this measure.

<sup>3.</sup> Current consumption is negligible and close to 0  $\mu$ A.

Table 40. Peripheral current consumption in Stop and Standby mode<sup>(1)</sup>

Symbol	Poriphoral	Typical consum	ption, T <sub>A</sub> = 25 °C	- Unit
Symbol	Peripheral	V <sub>DD</sub> =1.8 V	V <sub>DD</sub> =3.0 V	J
I <sub>DD(PVD / BOR)</sub>	-	0.7	1.2	
I <sub>REFINT</sub>	-	-	1.7	
-	LSE Low drive <sup>(2)</sup>	0.11	0,13	
-	LSI	0.27	0.31	
-	IWDG	0.2	0.3	
-	LPTIM1, Input 100 Hz	0.01	0,01	μΑ
-	LPTIM1, Input 1 MHz	11	12	
-	LPUART1	-	0,5	
-	RTC	0.16	0,3	

<sup>1.</sup> LPTIM, LPUART peripherals can operate in Stop mode but not in Standby mode.

## 6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 25*.

Table 41. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Тур	Max	Unit
t <sub>WUSLEEP</sub>	Wakeup from Sleep mode	f <sub>HCLK</sub> = 32 MHz	7	8	
	Wakeup from Low-power sleep mode,	f <sub>HCLK</sub> = 262 kHz Flash memory enabled	7	8	Number of clock
LP	f <sub>HCLK</sub> = 262 kHz	f <sub>HCLK</sub> = 262 kHz Flash memory switched OFF	9	10	cycles



LSE Low drive consumption is the difference between an external clock on OSC32\_IN and a quartz between OSC32\_IN and OSC32\_OUT.-

Table 41. Low-power mode wakeup timings (continued)

Symbol	Parameter	Conditions	Тур	Max	Unit
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 4.2 MHz	5.0	8	
	Wakeup from Stop mode, regulator in Run mode	f <sub>HCLK</sub> = f <sub>HSI</sub> = 16 MHz	4.9	7	
		$f_{HCLK} = f_{HSI}/4 = 4 \text{ MHz}$	8.0	11	
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 4.2 MHz Voltage range 1	5.0	8	
	\\ \frac{\damper{\lambda}}{\tau_i}	f <sub>HCLK</sub> = f <sub>MSI</sub> = 4.2 MHz Voltage range 2	5.0	8	
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 4.2 MHz Voltage range 3	5.0	8	
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 2.1 MHz	7.3	13	
t <sub>WUSTOP</sub>	power mode	f <sub>HCLK</sub> = f <sub>MSI</sub> = 1.05 MHz	13	23	
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 524 kHz	28	38	μs
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 262 kHz	51	65	
		f <sub>HCLK</sub> = f <sub>MSI</sub> = 131 kHz	100	120	
		f <sub>HCLK</sub> = MSI = 65 kHz	190	260	
		f <sub>HCLK</sub> = f <sub>HSI</sub> = 16 MHz	4.9	7	
		f <sub>HCLK</sub> = f <sub>HSI</sub> /4 = 4 MHz	8.0	11	
		f <sub>HCLK</sub> = f <sub>HSI</sub> = 16 MHz	4.9	7	
	Wakeup from Stop mode, regulator in low- power mode, code running from RAM	f <sub>HCLK</sub> = f <sub>HSI</sub> /4 = 4 MHz	7.9	10	
	3	f <sub>HCLK</sub> = f <sub>MSI</sub> = 4.2 MHz	4.7	8	
tunion	Wakeup from Standby mode FWU bit = 1	f <sub>HCLK</sub> = MSI = 2.1 MHz	65	130	
twustdby	Wakeup from Standby mode FWU bit = 0	f <sub>HCLK</sub> = MSI = 2.1 MHz	2.2	3	ms



#### 6.3.6 **External clock source characteristics**

## High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in Section 6.3.12. However, the recommended clock input waveform is shown in Figure 20.

Table 42. High-speed external user clock characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	User external clock source	CSS is ON or PLL is used	1	8	32	MHz
f <sub>HSE_ext</sub>	frequency	CSS is OFF, PLL not used	0	8	32	MHz
V <sub>HSEH</sub>	OSC_IN input pin high level voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage		V <sub>SS</sub>	ı	0.3V <sub>DD</sub>	٧
$\begin{array}{c} t_{\text{w(HSE)}} \\ t_{\text{w(HSE)}} \end{array}$	OSC_IN high or low time		12	ı	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time	-	-	-	20	113
C <sub>in(HSE)</sub>	OSC_IN input capacitance		-	2.6	-	pF
DuCy <sub>(HSE)</sub>	Duty cycle		45	ı	55	%
IL	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μA

<sup>1.</sup> Guaranteed by design.

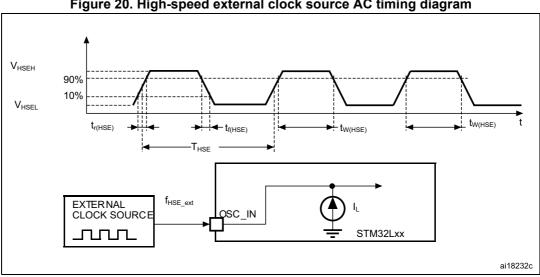


Figure 20. High-speed external clock source AC timing diagram

## Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a lowspeed external clock source, and under ambient temperature and supply voltage conditions summarized in Table 25.

Table 43. Low-speed external user clock characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSE_ext</sub>	User external clock source frequency		1	32.768	1000	kHz
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	-	V <sub>SS</sub>	-	0.3V <sub>DD</sub>	V
t <sub>w(LSE)</sub>	OSC32_IN high or low time		465	-	-	ns
$\begin{matrix} t_{r(LSE)} \\ t_{f(LSE)} \end{matrix}$	OSC32_IN rise or fall time		-	-	10	113
C <sub>IN(LSE)</sub>	OSC32_IN input capacitance	-	-	0.6	-	pF
DuCy <sub>(LSE)</sub>	Duty cycle	-	45	-	55	%
IL	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	μΑ

<sup>1.</sup> Guaranteed by design, not tested in production

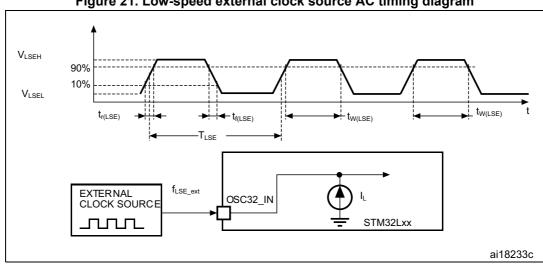


Figure 21. Low-speed external clock source AC timing diagram

### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 44*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>OSC_IN</sub>	Oscillator frequency	-	1		25	MHz
R <sub>F</sub>	Feedback resistor	-	-	200	-	kΩ
G <sub>m</sub>	Maximum critical crystal transconductance	Startup	-	-	700	μA /V
t <sub>SU(HSE)</sub>	Startup time	V <sub>DD</sub> is stabilized	ı	2	1	ms

Table 44. HSE oscillator characteristics<sup>(1)</sup>

For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 22*).  $C_{L1}$  and  $C_{L2}$  are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing  $C_{L1}$  and  $C_{L2}$ . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website *www.st.com*.

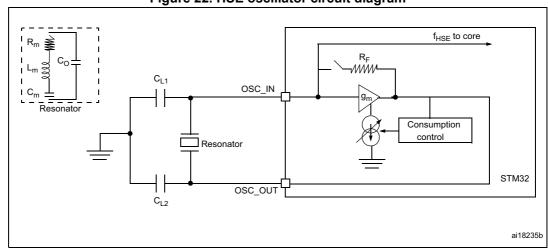


Figure 22. HSE oscillator circuit diagram

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<sup>1.</sup> Guaranteed by design.

Guaranteed by characterization results. t<sub>SU(HSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

### Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 45*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions <sup>(2)</sup>	Min <sup>(2)</sup>	Тур	Max	Unit
$f_{LSE}$	LSE oscillator frequency		-	32.768	-	kHz
		LSEDRV[1:0]=00 lower driving capability	-	-	0.5	
G	Maximum critical crystal	LSEDRV[1:0]= 01 medium low driving capability	-	-	0.75	uA/V
G <sub>m</sub>	transconductance	LSEDRV[1:0] = 10 medium high driving capability	-	-	1.7	μΑνν
		LSEDRV[1:0]=11 higher driving capability	-	-	2.7	
t <sub>SU(LSE)</sub> <sup>(3)</sup>	Startup time	V <sub>DD</sub> is stabilized	-	2	-	s

Table 45. LSE oscillator characteristics<sup>(1)</sup>

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

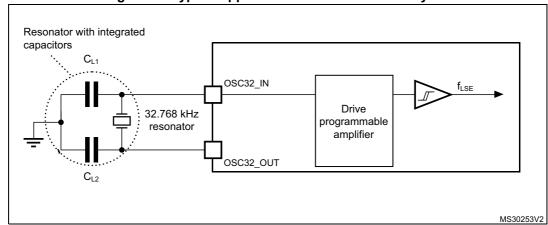


Figure 23. Typical application with a 32.768 kHz crystal

Note:

An external resistor is not required between OSC32\_IN and OSC32\_OUT and it is forbidden to add one.



<sup>1.</sup> Guaranteed by design.

Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".

Guaranteed by characterization results. t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer. To increase speed, address a lower-drive quartz with a high- driver mode.

### 6.3.7 Internal clock source characteristics

The parameters given in *Table 46* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 25*.

## High-speed internal 16 MHz (HSI16) RC oscillator

Table 46. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSI16</sub>	Frequency	V <sub>DD</sub> = 3.0 V	-	16	-	MHz
TRIM <sup>(1)(2)</sup>	HSI16 user-	Trimming code is not a multiple of 16	-	±0.4	0.7	%
TRIM	trimmed resolution	Trimming code is a multiple of 16	-	-	±1.5	%
		$V_{DDA}$ = 3.0 V, $T_A$ = 25 °C	-1 <sup>(3)</sup>	-	1 <sup>(3)</sup>	%
		$V_{DDA} = 3.0 \text{ V}, T_A = 0 \text{ to } 55 ^{\circ}\text{C}$	-1.5	-	1.5	%
۸۵۵	Accuracy of the	$V_{DDA}$ = 3.0 V, $T_A$ = -10 to 70 °C	-2	-	2	%
ACC <sub>HSI16</sub>	factory-calibrated HSI16 oscillator	$V_{DDA}$ = 3.0 V, $T_{A}$ = -10 to 85 °C	-2.5	-	2	%
	TIOTTO OSCINATO	$V_{DDA}$ = 3.0 V, $T_{A}$ = -10 to 105 °C	-4	-	2	%
		V <sub>DDA</sub> = 1.65 V to 3.6 V T <sub>A</sub> = -40 to 125 °C	-5.45	-	3.25	%
t <sub>SU(HSI16)</sub> <sup>(2)</sup>	HSI16 oscillator startup time	-		3.7	6	μs
I <sub>DD(HSI16)</sub> <sup>(2)</sup>	HSI16 oscillator power consumption	-	ı	100	140	μΑ

<sup>1.</sup> The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).

- 2. Guaranteed by characterization results.
- 3. Guaranteed by test in production.

Figure 24. HSI16 minimum and maximum value versus temperature 4.009 3.00% 2.00% 1.65V min 0,00 3V typ 60 20 40 120 3.6V max 1.65V max ■ 3.6V min 4 00 -5.00% -6.00% MSv34791V1

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# Low-speed internal (LSI) RC oscillator

Table 47. LSI oscillator characteristics

Symbol	Parameter	Min	Тур	Max	Unit
f <sub>LSI</sub> <sup>(1)</sup>	LSI frequency	26	38	56	kHz
D <sub>LSI</sub> <sup>(2)</sup>	LSI oscillator frequency drift 0°C ≤T <sub>A</sub> ≤85°C	-10	-	4	%
t <sub>su(LSI)</sub> <sup>(3)</sup>	LSI oscillator startup time	-	-	200	μs
I <sub>DD(LSI)</sub> (3)	LSI oscillator power consumption	-	400	510	nA

- 1. Guaranteed by test in production.
- 2. This is a deviation for an individual part, once the initial frequency has been measured.
- 3. Guaranteed by design.

# Multi-speed internal (MSI) RC oscillator

Table 48. MSI oscillator characteristics

Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	65.5	-	
		MSI range 1	131	-	kHz
		MSI range 2	262	-	KI IZ
f <sub>MSI</sub>	Frequency after factory calibration, done at $V_{DD}$ = 3.3 V and $T_A$ = 25 °C	MSI range 3	524	-	
		MSI range 4	1.05	-	
		MSI range 5	2.1	-	MHz
		MSI range 6	4.2	-	1
ACC <sub>MSI</sub>	Frequency error after factory calibration	-	±0.5	-	%
	MSI oscillator frequency drift 0 °C ≤T <sub>A</sub> ≤85 °C	-	±3	-	
		MSI range 0	- 8.9	+7.0	
		MSI range 1	- 7.1	+5.0	
D <sub>TEMP(MSI)</sub> <sup>(1)</sup>		MSI range 2	- 6.4	+4.0	%
( - )	MSI oscillator frequency drift V <sub>DD</sub> = 3.3 V, − 40 °C ≤T <sub>A</sub> ≤110 °C	MSI range 3	- 6.2	+3.0	
	TOD STORY TO SERVE S	MSI range 4	- 5.2	+3.0	
		MSI range 5	- 4.8	+2.0	
		MSI range 6	- 4.7	+2.0	
D <sub>VOLT(MSI)</sub> <sup>(1)</sup>	MSI oscillator frequency drift 1.65 V ≤V <sub>DD</sub> ≤3.6 V, T <sub>A</sub> = 25 °C	-	-	2.5	%/V



Table 48. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Тур	Max	Unit
		MSI range 0	0.75	-	
		MSI range 1	1	-	
		MSI range 2	1.5	-	
I <sub>DD(MSI)</sub> <sup>(2)</sup>	MSI oscillator power consumption	MSI range 3	2.5	-	μΑ
		MSI range 4	4.5	-	
		MSI range 5	8	-	
		MSI range 6	15	-	
		MSI range 0	30	0.75 - 1 - 1.5 - 2.5 - 4.5 - 8 - 15 -	
		MSI range 1	20	-	
	MSI oscillator startup time	MSI range 2	15	-	
		MSI range 3	10	-	
4		MSI range 4	6	-	μs
t <sub>SU(MSI)</sub>		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
		MSI range 0	-	40	
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
t <sub>STAB(MSI)</sub> <sup>(2)</sup>	MSI oscillator stabilization time	MSI range 4	-	2.5	μs
STAB(MSI)	Wor oscillator stabilization time	MSI range 5	-	2	μο
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
fo	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
f <sub>OVER(MSI)</sub>	Mor oscillator frequency overshoot	Any range to range 6	-	6	IVII IZ

<sup>1.</sup> This is a deviation for an individual part, once the initial frequency has been measured.

<sup>2.</sup> Guaranteed by characterization results.

### 6.3.8 PLL characteristics

The parameters given in *Table 49* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 25*.

Table 49. PLL characteristics

Symbol	Parameter		Unit		
Symbol	Symbol Farameter		Тур	Max <sup>(1)</sup>	Unit
t	PLL input clock <sup>(2)</sup>	2	-	24	MHz
f <sub>PLL_IN</sub>	PLL input clock duty cycle	45	-	55	%
f <sub>PLL_OUT</sub>	PLL output clock	2	-	32	MHz
t <sub>LOCK</sub>	PLL input = 16 MHz PLL VCO = 96 MHz	-	115	160	μs
Jitter	Cycle-to-cycle jitter	-		±600	ps
I <sub>DDA</sub> (PLL)	Current consumption on V <sub>DDA</sub>	-	220	450	
I <sub>DD</sub> (PLL)	Current consumption on V <sub>DD</sub>	-	120	150	μΑ

<sup>1.</sup> Guaranteed by characterization results.

## 6.3.9 Memory characteristics

### **RAM** memory

Table 50. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VRM	Data retention mode <sup>(1)</sup>	STOP mode (or RESET)	1.65	-	-	V

Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

## Flash memory and data EEPROM

Table 51. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Тур	Max <sup>(1)</sup>	Unit
V <sub>DD</sub>	Operating voltage Read / Write / Erase	-	1.65	-	3.6	٧
t <sub>prog</sub>	Programming time for word or half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	1115

Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f<sub>PLL\_OUT</sub>.

Table 51. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Тур	Max <sup>(1)</sup>	Unit
	Average current during the whole programming / erase operation		-	500	700	μΑ
I <sub>DD</sub>	Maximum current (peak) during the whole programming / erase operation	T <sub>A</sub> = 25 °C, V <sub>DD</sub> = 3.6 V	-	1.5	2.5	mA

<sup>1.</sup> Guaranteed by design.

Table 52. Flash memory and data EEPROM endurance and retention

Cumhal	Davassatav	Conditions	Value	l lmi4
Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Unit
N <sub>CYC</sub> <sup>(2)</sup>	Cycling (erase / write) Program memory	T <sub>A</sub> = -40°C to 105 °C	10	
	Cycling (erase / write) EEPROM data memory	14 = 40 0 10 103 0	100	kcycles
	Cycling (erase / write) Program memory	T <sub>A</sub> = -40°C to 125 °C	0.2	RCYCICS
	Cycling (erase / write) EEPROM data memory	14 = -40 0 10 123 0	2	
	Data retention (program memory) after 10 kcycles at T <sub>A</sub> = 85 °C	T <sub>RET</sub> = +85 °C	30	
	Data retention (EEPROM data memory) after 100 kcycles at $T_A$ = 85 °C	TRET = 100 G	30	
t <sub>RET</sub> <sup>(2)</sup>	Data retention (program memory) after 10 kcycles at T <sub>A</sub> = 105 °C	-T <sub>RFT</sub> = +105 °C		years
'RET'	Data retention (EEPROM data memory) after 100 kcycles at T <sub>A</sub> = 105 °C	TRET - 1103 G	10	years
	Data retention (program memory) after 200 cycles at T <sub>A</sub> = 125 °C	T - +125 °C	10	
	Data retention (EEPROM data memory) after 2 kcycles at T <sub>A</sub> = 125 °C	T <sub>RET</sub> = +125 °C		

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> Characterization is done according to JEDEC JESD22-A117.

### 6.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 53*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/ Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD}$ = 3.3 V, LQFP100, $T_{A}$ = +25 °C, $f_{HCLK}$ = 32 MHz conforms to IEC 61000-4-2	3B
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100 pF on V <sub>DD</sub> and V <sub>SS</sub> pins to induce a functional disturbance	$V_{DD}=3.3$ V, LQFP100, $T_{A}=+25$ °C, $f_{HCLK}=32$ MHz conforms to IEC 61000-4-4	4A

Table 53. EMS characteristics

### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.



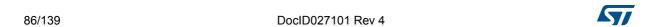
To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

## **Electromagnetic Interference (EMI)**

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

**Table 54. EMI characteristics** 

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. frequency range at 32 MHz	Unit
	Peak level $V_{DD} = 3.6 \text{ V},$ $T_A = 25 ^{\circ}\text{C},$ LQFP100 package compliant with IEC 61	$V_{DD} = 3.6 \text{ V},$	0.1 to 30 MHz	-7	
9			30 to 130 MHz	14	dΒμV
S <sub>EMI</sub>		LQFP100 package	130 MHz to 1 GHz	9	
		compliant with IEC 61967-2	EMI Level	2	-



## 6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 55. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value <sup>(1)</sup>	Unit
V <sub>ESD(HBM)</sub>	Electrostatic discharge voltage (human body model)	T <sub>A</sub> = +25 °C, conforming to ANSI/JEDEC JS-001	2	2000	V
V <sub>ESD(CDM)</sub>	Electrostatic discharge voltage (charge device model)	T <sub>A</sub> = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	V

<sup>1.</sup> Guaranteed by characterization results.

### Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 56. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T <sub>A</sub> = +125 °C conforming to JESD78A	II level A

#### 6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V<sub>SS</sub> or above V<sub>DD</sub> (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

### Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of -5 µA/+0 µA range), or other functional failure (for example reset occurrence oscillator frequency deviation).

The test results are given in the *Table 57*.

Table 57. I/O current injection susceptibility

		Functional s		
Symbol	Description	Negative injection	Positive injection	Unit
	Injected current on BOOT0	-0	NA <sup>(1)</sup>	
I <sub>INJ</sub>	Injected current on PA0, PA4, PA5, PC15, PH0 and PH1	-5	0	mA
	Injected current on any other FT, FTf pins	-5 <sup>(2)</sup>	NA <sup>(1)</sup>	
	Injected current on any other pins	-5 <sup>(2)</sup>	+5	

<sup>1.</sup> Current injection is not possible.

<sup>2.</sup> It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

# 6.3.13 I/O port characteristics

## General input/output characteristics

Unless otherwise specified, the parameters given in *Table 58* are derived from tests performed under the conditions summarized in *Table 25*. All I/Os are CMOS and TTL compliant.

Table 58. I/O static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL</sub>	Input low level voltage	TC, FT, FTf, RST I/Os	-	-	0.3V <sub>DD</sub>	
	-	BOOT0 pin	-	-	0.14V <sub>DD</sub> <sup>(1)</sup>	
V <sub>IH</sub>	Input high level voltage	All I/Os	0.7 V <sub>DD</sub>	-	-	V
V	I/O Schmitt trigger voltage hysteresis	Standard I/Os	-	10% V <sub>DD</sub> <sup>(3)</sup>	-	
V <sub>hys</sub>	(2)	BOOT0 pin	-	0.01	-	
		V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	±50	
	Input leakage current <sup>(4)</sup>	V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> , PA11 and PA12 I/Os	-	-	-50/+250	nA
		V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> FTf I/Os	-	-	±100	
I <sub>lkg</sub>		V <sub>DD</sub> ≤V <sub>IN</sub> ≤5 V All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	200	nA
		V <sub>DD</sub> ≤V <sub>IN</sub> ≤5 V FTf I/Os	-	-	500	
		V <sub>DD</sub> ≤V <sub>IN</sub> ≤5 V PA11, PA12 and BOOT0	-	-	10	μΑ
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(5)</sup>	$V_{IN} = V_{SS}$	25	45	65	kΩ
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(5)</sup>	$V_{IN} = V_{DD}$	25	45	65	kΩ
C <sub>IO</sub>	I/O pin capacitance	-	-	5	-	pF

<sup>1.</sup> Guaranteed by characterization.

<sup>2.</sup> Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

<sup>3.</sup> With a minimum of 200 mV. Guaranteed by characterization results.

<sup>4.</sup> The max. value may be exceeded if negative current is injected on adjacent pins.

Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

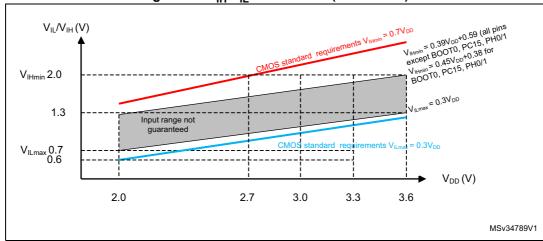
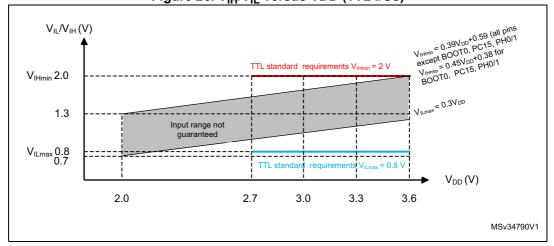


Figure 25. V<sub>IH</sub>/V<sub>IL</sub> versus VDD (CMOS I/Os)

Figure 26. V<sub>IH</sub>/V<sub>IL</sub> versus VDD (TTL I/Os)



### **Output driving current**

The GPIOs (general purpose input/outputs) can sink or source up to  $\pm 8$  mA, and sink or source up to  $\pm 15$  mA with the non-standard  $V_{OL}/V_{OH}$  specifications given in *Table 59*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V<sub>DD</sub>, plus the maximum Run consumption of the MCU sourced on V<sub>DD</sub>, cannot exceed the absolute maximum rating I<sub>VDD</sub>(Σ) (see *Table 23*).
- The sum of the currents sunk by all the I/Os on V<sub>SS</sub> plus the maximum Run consumption of the MCU sunk on V<sub>SS</sub> cannot exceed the absolute maximum rating I<sub>VSS(Σ)</sub> (see *Table 23*).

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## **Output voltage levels**

Unless otherwise specified, the parameters given in *Table 59* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 25*. All I/Os are CMOS and TTL compliant.

Table 59. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>OL</sub> <sup>(1)</sup>	Output low level voltage for an I/O pin	CMOS port <sup>(2)</sup> ,	-	0.4	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}$	V <sub>DD</sub> -0.4	-	
V <sub>OL</sub> <sup>(1)</sup>	Output low level voltage for an I/O pin	TTL port <sup>(2)</sup> , $I_{IO} = + 8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	
V <sub>OH</sub> (3)(4)	Output high level voltage for an I/O pin	TTL port <sup>(2)</sup> , $I_{IO} = -6 \text{ mA}$ $2.7 \text{ V} \le V_{DD} \le 3.6 \text{ V}$	2.4	-	
V <sub>OL</sub> <sup>(1)(4)</sup>	Output low level voltage for an I/O pin	$I_{IO}$ = +15 mA 2.7 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	-	1.3	٧
V <sub>OH</sub> <sup>(3)(4)</sup>	Output high level voltage for an I/O pin	$I_{IO}$ = -15 mA 2.7 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	V <sub>DD</sub> -1.3	-	
V <sub>OL</sub> <sup>(1)(4)</sup>	Output low level voltage for an I/O pin	I <sub>IO</sub> = +4 mA 1.65 V ≤V <sub>DD</sub> < 3.6 V	-	0.45	
V <sub>OH</sub> <sup>(3)(4)</sup>	Output high level voltage for an I/O pin	$I_{IO} = -4 \text{ mA}$ 1.65 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	V <sub>DD</sub> -0.45	-	
V (1)(4)	Output low level voltage for an FTf I/O pin in Fm+ mode	$I_{IO} = 20 \text{ mA}$ 2.7 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	-	0.4	
V <sub>OLFM+</sub> (1)(4)		$I_{IO}$ = 10 mA 1.65 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	-	0.4	

The I<sub>IO</sub> current sunk by the device must always respect the absolute maximum rating specified in *Table 23*.
The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed ΣI<sub>IO(PIN)</sub>.

<sup>2.</sup> TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.

The I<sub>IO</sub> current sourced by the device must always respect the absolute maximum rating specified in Table 23. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed ΣI<sub>IO(PIN)</sub>.

<sup>4.</sup> Guaranteed by characterization results.

### Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 27* and *Table 60*, respectively.

Unless otherwise specified, the parameters given in *Table 60* are derived from tests performed under ambient temperature and V<sub>DD</sub> supply voltage conditions summarized in *Table 25*.

Table 60. I/O AC characteristics<sup>(1)</sup>

OSPEEDRx[1:0] bit value <sup>(1)</sup>	Symbol	Parameter	Conditions	Min	Max <sup>(2)</sup>	Unit
	f	Maximum frequency <sup>(3)</sup>	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	400	kHz
00	f <sub>max(IO)out</sub>	waximum frequency.	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	100	KIIZ
00	t <sub>f(IO)out</sub>	Output rise and fall time	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	125	ns
	t <sub>r(IO)out</sub>	Output rise and fail time	$C_L = 50 \text{ pF}, V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	320	113
	f	Maximum frequency <sup>(3)</sup>	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	2	MHz
01	f <sub>max(IO)out</sub>	waximum nequency	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	0.6	IVIIIZ
01	t <sub>f(IO)out</sub>	Output rise and fall time	$C_L = 50 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	30	ns
	t <sub>r(IO)out</sub>	Output rise and fail time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	65	115
	F	Maximum frequency <sup>(3)</sup>	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 2.7 V to 3.6 V	-	10	MHz
10	F <sub>max(IO)out</sub>	waximum frequency.	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	2	IVITZ
10	t <sub>f(IO)out</sub>	Output rice and fall time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 2.7 V to 3.6 V	-	13	ns
	t <sub>r(IO)out</sub>	Output rise and fall time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	28	118
	Е	Maximum frequency <sup>(3)</sup>	$C_L = 30 \text{ pF}, V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	35	MHz
11	F <sub>max(IO)out</sub>	waximum frequency.	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	10	IVITZ
11	t <sub>f(IO)out</sub>	Output rise and fall time	C <sub>L</sub> = 30 pF, V <sub>DD</sub> = 2.7 V to 3.6 V	- 6		no
	t <sub>r(IO)out</sub>	Output rise and fail time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 2.7 V	-	17	ns
	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		-	1	MHz
	t <sub>f(IO)out</sub>	Output fall time	$C_L = 50 \text{ pF}, V_{DD} = 2.5 \text{ V to } 3.6 \text{ V}$	-	10	no
Fm+	t <sub>r(IO)out</sub>	Output rise time		-	30	ns
configuration <sup>(4)</sup>	f <sub>max(IO)out</sub>	Maximum frequency <sup>(3)</sup>		-	350	KHz
	t <sub>f(IO)out</sub>	Output fall time	C <sub>L</sub> = 50 pF, V <sub>DD</sub> = 1.65 V to 3.6 V	-	15	
	t <sub>r(IO)out</sub>	Output rise time		-	60	ns
-	t <sub>EXTIpw</sub>	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

<sup>1.</sup> The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.

<sup>2.</sup> Guaranteed by design.

<sup>3.</sup> The maximum frequency is defined in Figure 27.

<sup>4.</sup> When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

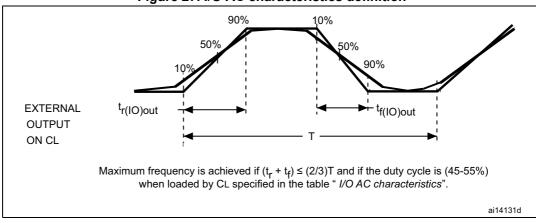


Figure 27. I/O AC characteristics definition

## 6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R<sub>PU</sub>, except when it is internally driven low (see *Table 61*).

Unless otherwise specified, the parameters given in *Table 61* are derived from tests performed under ambient temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 25*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST input low level voltage	-	$V_{SS}$	-	8.0	
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST input high level voltage	-	1.4	-	$V_{DD}$	
V <sub>2</sub> , ,,,,,,,,,(1)	NRST output low level	I <sub>OL</sub> = 2 mA 2.7 V < V <sub>DD</sub> < 3.6 V	ı	1	0.4	V
V <sub>OL(NRST)</sub> <sup>(1)</sup>	voltage	I <sub>OL</sub> = 1.5 mA 1.65 V < V <sub>DD</sub> < 2.7 V	-	-	0.4	
V <sub>hys(NRST)</sub> <sup>(1)</sup>	NRST Schmitt trigger voltage hysteresis	-	-	10%V <sub>DD</sub> <sup>(2)</sup>	ı	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(3)</sup>	$V_{IN} = V_{SS}$	25	45	65	kΩ
V <sub>F(NRST)</sub> <sup>(1)</sup>	NRST input filtered pulse	-	-	-	50	ns
V <sub>NF(NRST)</sub> <sup>(1)</sup>	NRST input not filtered pulse	-	350	-	-	ns

Table 61. NRST pin characteristics

<sup>1.</sup> Guaranteed by design.

<sup>2. 200</sup> mV minimum value

<sup>3.</sup> The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

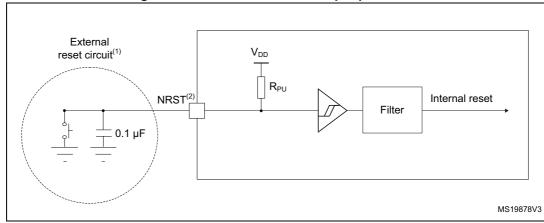


Figure 28. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets.
- 2. The external capacitor must be placed as close as possible to the device.
- The user must ensure that the level on the NRST pin can go below the V<sub>IL(NRST)</sub> max level specified in Table 61. Otherwise the reset will not be taken into account by the device.

### 6.3.15 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 62* are derived from tests performed under ambient temperature, f<sub>PCLK</sub> frequency and V<sub>DDA</sub> supply voltage conditions summarized in *Table 25: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

**Table 62. ADC characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V	Analog supply voltage for	Fast channel	1.65	-	3.6	V	
$V_{DDA}$	ADC ON	Standard channel	1.75 <sup>(1)</sup>	-	3.6	V	
V <sub>REF+</sub>	Positive reference voltage	-	1.65		$V_{DDA}$	V	
V <sub>REF-</sub>	Negative reference voltage	-	-	0	-		
I <sub>DDA (ADC)</sub>	Current consumption of the	1.14 Msps	-	200	-		
	ADC on V <sub>DDA</sub> and V <sub>REF+</sub>	10 ksps	-	40	-	μΑ	
	Current consumption of the ADC on ${\rm V_{DD}}^{(2)}$	1.14 Msps	-	70	-	μΑ	
		10 ksps	-	1	-		
		Voltage scaling Range 1	0.14	-	16		
$f_{ADC}$	ADC clock frequency	Voltage scaling Range 2	0.14	-	8	MHz	
		Voltage scaling Range 3	0.14	-	4		
f <sub>S</sub> <sup>(3)</sup>	Sampling rate	12-bit resolution	0.01	-	1.14	MHz	
f <sub>TRIG</sub> <sup>(3)</sup>	External trigger frequency	f <sub>ADC</sub> = 16 MHz, 12-bit resolution	-	-	941	kHz	
1140		-	-	-	17	1/f <sub>ADC</sub>	
V <sub>AIN</sub>	Conversion voltage range	-	0	-	V <sub>REF+</sub>	V	

Table 62. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>AIN</sub> <sup>(3)</sup>	External input impedance	See Equation 1 and Table 63 for details	-	-	50	kΩ
R <sub>ADC</sub> (3)(4)	Sampling switch resistance	-	-	-	1	kΩ
C <sub>ADC</sub> <sup>(3)</sup>	Internal sample and hold capacitor	-	-	-	8	pF
t <sub>CAL</sub> (3)(5)	Calibration time	f <sub>ADC</sub> = 16 MHz		5.2		μs
'CAL'	Calibration time	-	- 83			1/f <sub>ADC</sub>
W <sub>LATENCY</sub> <sup>(6)</sup>		ADC clock = HSI16	1.5 ADC cycles + 2 f <sub>PCLK</sub> cycles	-	1.5 ADC cycles + 3 f <sub>PCLK</sub> cycles	-
		ADC clock = PCLK/2	-	4.5	-	f <sub>PCLK</sub> cycle
		ADC clock = PCLK/4	-	8.5	-	f <sub>PCLK</sub> cycle
		$f_{ADC} = f_{PCLK}/2 = 16 \text{ MHz}$		0.266		μs
		$f_{ADC} = f_{PCLK}/2$	8.5		1/f <sub>PCLK</sub>	
t <sub>latr</sub> (3)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/4 = 8 \text{ MHz}$	0.516		μs	
		$f_{ADC} = f_{PCLK}/4$	16.5		1/f <sub>PCLK</sub>	
		$f_{ADC} = f_{HSI16} = 16 \text{ MHz}$	0.252	1	0.260	μs
Jitter <sub>ADC</sub>	ADC jitter on trigger conversion	f <sub>ADC</sub> = f <sub>HSI16</sub>	-	1	-	1/f <sub>HSI16</sub>
t <sub>S</sub> <sup>(3)</sup>	Sampling time	f <sub>ADC</sub> = 16 MHz	0.093	-	10.03	μs
ıs.	Sampling time	-	1.5	-	160.5	1/f <sub>ADC</sub>
t <sub>UP_LDO</sub> (3)(5)	Internal LDO power-up time	-	-	-	10	μs
t <sub>STAB</sub> (3)(5)	ADC stabilization time	-		14		1/f <sub>ADC</sub>
+ (3)	Total conversion time	f <sub>ADC</sub> = 16 MHz, 12-bit resolution	0.875	-	10.81	μs
t <sub>ConV</sub> <sup>(3)</sup>	(including sampling time)	12-bit resolution	14 to 173 (t <sub>S</sub> for sampling +12.5 for successive approximation)			1/f <sub>ADC</sub>

<sup>1.</sup> V<sub>DDA</sub> minimum value can be decreased in specific temperature conditions. Refer to *Table 63: RAIN max for fADC = 16 MHz*.

<sup>2.</sup> A current consumption proportional to the APB clock frequency has to be added (see *Table 39: Peripheral current consumption in Run or Sleep mode*).

<sup>3.</sup> Guaranteed by design.

Standard channels have an extra protection resistance which depends on supply voltage. Refer to Table 63: RAIN max for fADC = 16 MHz.

<sup>5.</sup> This parameter only includes the ADC timing. It does not take into account register access latency.

<sup>6.</sup> This parameter specifies the latency to transfer the conversion result into the ADC\_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

## Equation 1: R<sub>AIN</sub> max formula

$$R_{AIN} < \frac{T_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The simplified formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

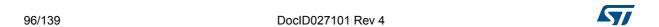
Table 63.  $R_{AIN}$  max for  $f_{ADC} = 16 \text{ MHz}^{(1)}$ 

			$R_{AIN}$ max for standard channels (kΩ)							
T <sub>s</sub> (cycles)	t <sub>S</sub> (µs)		V <sub>DD</sub> > 2.7 V	V <sub>DD</sub> > 2.4 V	V <sub>DD</sub> > 2.0 V	V <sub>DD</sub> > 1.8 V	V <sub>DD</sub> > 1.75 V	V <sub>DD</sub> > 1.65 V and T <sub>A</sub> > -10 °C	V <sub>DD</sub> > 1.65 V and T <sub>A</sub> > 25 °C	
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA	
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA	
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA	
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA	
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1	
39.5	2.47	13	12.2	12	10	NA	NA	NA	5	
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19	
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42	

<sup>1.</sup> Guaranteed by design.

Table 64. ADC accuracy<sup>(1)(2)(3)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ET	Total unadjusted error		-	2	4	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.5	
	Effective number of bits	1.65 V < V <sub>DDA</sub> = V <sub>REF+</sub> < 3.6 V,	10.2	11		
ENOB	Effective number of bits (16-bit mode oversampling with ratio =256) <sup>(4)</sup>	range 1/2/3	11.3	12.1	-	bits
SINAD	Signal-to-noise distortion		63	69	-	
	Signal-to-noise ratio		63	69	-	
SNR	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) <sup>(4)</sup>		70	76	-	dB
THD	Total harmonic distortion		-	-85	-73	



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ET	Total unadjusted error		-	2	5	
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	LSB
EL	Integral linearity error		-	1.5	3	
ED	Differential linearity error	1.65 V < V <sub>REF+</sub> <v<sub>DDA &lt; 3.6 V, range 1/2/3</v<sub>	-	1	2	
ENOB	Effective number of bits		10.0	11.0	-	bits
SINAD	Signal-to-noise distortion		62	69	-	
SNR	Signal-to-noise ratio		61	69	-	dB
THD	Total harmonic distortion		-	-85	-65	

Table 64. ADC accuracy<sup>(1)(2)(3)</sup> (continued)

- 1. ADC DC accuracy values are measured after internal calibration.
- ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for I<sub>INJ(PIN)</sub> and ΣI<sub>INJ(PIN)</sub> in Section 6.3.12 does not affect the ADC accuracy.
- 3. Better performance may be achieved in restricted V<sub>DDA</sub>, frequency and temperature ranges.
- 4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.

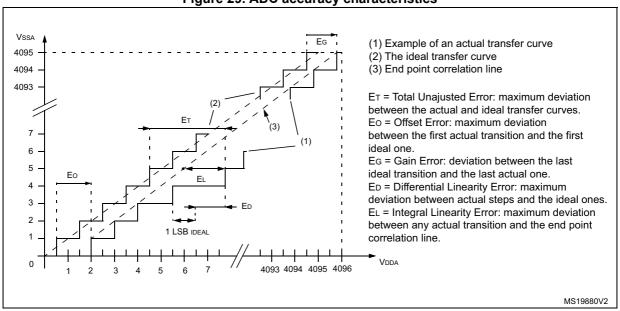


Figure 29. ADC accuracy characteristics

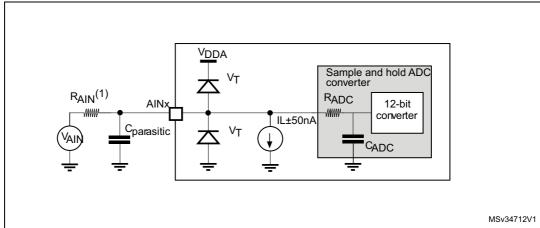


Figure 30. Typical connection diagram using the ADC

- 1. Refer to Table 62: ADC characteristics for the values of RAIN, RADC and CADC.
- $C_{parasitic}$  represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high  $C_{parasitic}$  value will downgrade conversion accuracy. To remedy this,  $f_{ADC}$  should be reduced.

## General PCB design guidelines

Power supply decoupling should be performed as shown in Figure 31 or Figure 32, depending on whether  $V_{\text{REF+}}$  is connected to  $V_{\text{DDA}}$  or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

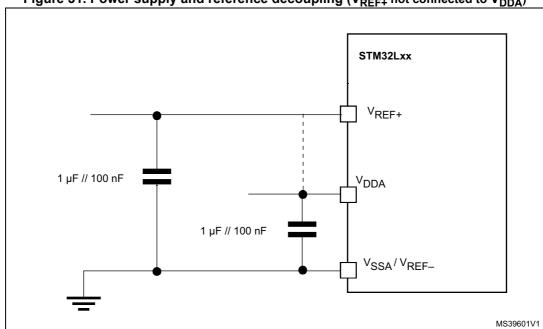


Figure 31. Power supply and reference decoupling ( $V_{REF+}$  not connected to  $V_{DDA}$ )

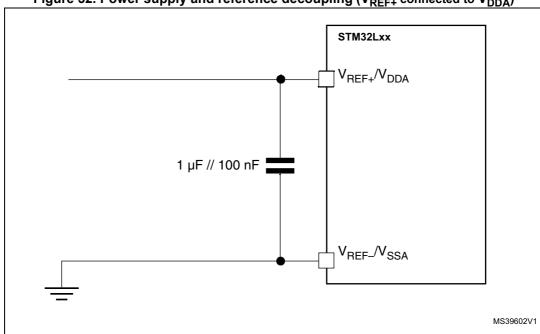


Figure 32. Power supply and reference decoupling ( $V_{REF+}$  connected to  $V_{DDA}$ )

## 6.3.16 Temperature sensor characteristics

Table 65. Temperature sensor calibration values

Calibration value name	Description	Memory address		
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V <sub>DDA</sub> = 3 V	0x1FF8 007A - 0x1FF8 007B		
TS_CAL2	TS ADC raw data acquired at temperature of 130 °C, V <sub>DDA</sub> = 3 V	0x1FF8 007E - 0x1FF8 007F		

Table 66. Temperature sensor characteristics

Symbol	Parameter	Min	Тур	Max	Unit
$T_{L}^{(1)}$	V <sub>SENSE</sub> linearity with temperature	-	±1	<u>+2</u>	°C
Avg_Slope <sup>(1)</sup>	Average slope	1.48	1.61	1.75	mV/°C
V <sub>130</sub>	Voltage at 130°C ±5°C <sup>(2)</sup>	640	670	700	mV
I <sub>DDA(TEMP)</sub> (3)	Current consumption	-	3.4	6	μA
t <sub>START</sub> (3)	Startup time	-	-	10	116
T <sub>S_temp</sub> (4)(3)	ADC sampling time when reading the temperature	10	-	-	μs

- 1. Guaranteed by characterization results.
- 2. Measured at  $V_{DD}$  = 3 V ±10 mV. V130 ADC conversion result is stored in the TS\_CAL2 byte.
- 3. Guaranteed by design.
- 4. Shortest sampling time can be determined in the application by multiple iterations.

# 6.3.17 Comparators

Table 67. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
$V_{DDA}$	Analog supply voltage	-	1.65		3.6	V
R <sub>400K</sub>	R <sub>400K</sub> value	-	-	400	-	kΩ
R <sub>10K</sub>	R <sub>10K</sub> value	-	-	10	-	K22
V <sub>IN</sub>	Comparator 1 input voltage range	-	0.6	-	$V_{DDA}$	V
t <sub>START</sub>	Comparator startup time	-	-	7	10	ue
td	Propagation delay <sup>(2)</sup>	-	-	3	10	μs
Voffset	Comparator offset	-	-	±3	±10	mV
d <sub>Voffset</sub> /dt	Comparator offset variation in worst voltage stress conditions	$\begin{split} V_{DDA} &= 3.6 \text{ V}, V_{IN+} = 0 \text{ V}, \\ V_{IN-} &= V_{REFINT}, T_A = 25 ^{\circ}\text{C} \end{split}$	0	1.5	10	mV/1000 h
I <sub>COMP1</sub>	Current consumption <sup>(3)</sup>	-	-	160	260	nA

<sup>1.</sup> Guaranteed by characterization.

Table 68. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max <sup>(1)</sup>	Unit	
$V_{DDA}$	Analog supply voltage	-	1.65	-	3.6	V	
V <sub>IN</sub>	Comparator 2 input voltage range	-	0	-	$V_{DDA}$	V	
+.	Comparator startup time	Fast mode	-	15	20		
t <sub>START</sub>	Comparator startup time	Slow mode	-	20	25		
+	Propagation delay <sup>(2)</sup> in slow mode	1.65 V ≤V <sub>DDA</sub> ≤2.7 V	-	1.8	3.5	116	
<sup>t</sup> d slow	Propagation delay VIII slow mode	2.7 V ≤V <sub>DDA</sub> ≤3.6 V	-	2.5	6	μs	
4	Propagation delay <sup>(2)</sup> in fast mode	1.65 V ≤V <sub>DDA</sub> ≤2.7 V	-	0.8	2		
t <sub>d fast</sub>		2.7 V ≤V <sub>DDA</sub> ≤3.6 V	-	1.2	4		
V <sub>offset</sub>	Comparator offset error		-	±4	±20	mV	
dThreshold/ dt	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V$ , $T_A = 0$ to $50 ^{\circ}$ C, $V_{-} = V_{REFINT}$ , $3/4 ^{\vee}V_{REFINT}$ , $1/2 ^{\vee}V_{REFINT}$ , $1/4 ^{\vee}V_{REFINT}$ .	-	15	30	ppm /°C	
1	Current consumption <sup>(3)</sup>	Fast mode	-	3.5	5		
I <sub>COMP2</sub>	Current consumption,	Slow mode	-	0.5	2	μA	

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

<sup>3.</sup> Comparator consumption only. Internal reference voltage not included.

<sup>2.</sup> The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

<sup>3.</sup> Comparator consumption only. Internal reference voltage (required for comparator operation) is not included.

### 6.3.18 Timer characteristics

### **TIM timer characteristics**

The parameters given in the *Table 69* are guaranteed by design.

Refer to Section 6.3.13: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Max	Unit			
t	Timer resolution time		1	-	t <sub>TIMxCLK</sub>			
<sup>t</sup> res(TIM)	Time resolution time	f <sub>TIMxCLK</sub> = 32 MHz	31.25	-	ns			
· ·	Timer external clock frequency on CH1		0	f <sub>TIMxCLK</sub> /2	MHz			
f <sub>EXT</sub>	to CH4	f <sub>TIMxCLK</sub> = 32 MHz	0	16	MHz			
Res <sub>TIM</sub>	Timer resolution	-		16	bit			
	16-bit counter clock period when	-	1	65536	t <sub>TIMxCLK</sub>			
t <sub>COUNTER</sub>	internal clock is selected (timer's prescaler disabled)	f <sub>TIMxCLK</sub> = 32 MHz	0.0312	2048	μs			
	Maximum possible count	-	-	65536 × 65536	t <sub>TIMxCLK</sub>			
t <sub>MAX_COUNT</sub>	Iwaxiiiidiii possible coulit	f <sub>TIMxCLK</sub> = 32 MHz	-	134.2	S			

Table 69. TIMx characteristics<sup>(1)</sup>

### 6.3.19 Communications interfaces

## I<sup>2</sup>C interface characteristics

The  $I^2C$  interface meets the timings requirements of the  $I^2C$ -bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I<sup>2</sup>C timing requirements are guaranteed by design when the I<sup>2</sup>C peripheral is properly configured (refer to the reference manual for details). The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to Section 6.3.13: I/O port characteristics for the I2C I/Os characteristics).

All I<sup>2</sup>C SDA and SCL I/Os embed an analog filter (see *Table 70* for the analog filter characteristics).

<sup>1.</sup> TIMx is used as a general term to refer to the TIM2, TIM6, TIM21, and TIM22 timers.

The analog spike filter is compliant with I<sup>2</sup>C timings requirements only for the following voltage ranges:

- Fast mode Plus: 2.7 V ≤V<sub>DD</sub> ≤3.6 V and voltage scaling Range 1
- Fast mode:
  - 2 V ≤V<sub>DD</sub> ≤3.6 V and voltage scaling Range 1 or Range 2.
  - V<sub>DD</sub> < 2 V, voltage scaling Range 1 or Range 2, C<sub>load</sub> < 200 pF.</li>

In other ranges, the analog filter should be disabled. The digital filter can be used instead.

Note: In Standard mode, no spike filter is required.

Table 70. I2C analog filter characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit	
		Range 1		260 <sup>(3)</sup>		l
	Maximum pulse width of spikes that are suppressed by the analog filter	Range 2	50 <sup>(2)</sup>	-	ns	•
		Range 3		-		İ

- 1. Guaranteed by characterization results.
- 2. Spikes with widths below  $t_{AF(min)}$  are filtered.
- 3. Spikes with widths above  $t_{\text{AF}(\text{max})}$  are not filtered

### **SPI** characteristics

Unless otherwise specified, the parameters given in the following tables are derived from tests performed under ambient temperature,  $f_{PCLKx}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 25*.

Refer to Section 6.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 71. SPI characteristics in voltage Range 1 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode	Master mode	-	16	
	SPI clock frequency	Slave mode receiver	-		16	
f <sub>SCK</sub> 1/t <sub>c(SCK)</sub>		Slave mode Transmitter 1.71 <v<sub>DD&lt;3.6V</v<sub>	-	-	12 <sup>(2)</sup>	MHz
		Slave mode Transmitter 2.7 <v<sub>DD&lt;3.6V</v<sub>	-	-	16 <sup>(2)</sup>	
Duty <sub>(SCK)</sub>	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%



Table 71. SPI characteristics in voltage Range 1 (1) (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
$t_{w(SCKH)} \ t_{w(SCKL)}$	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+	
t <sub>su(MI)</sub>	Data in mut autum tima	Master mode	0	-	-	
t <sub>su(SI)</sub>	Data input setup time	Slave mode	3	-	-	
t <sub>h(MI)</sub>	Data input hold time	Master mode	7	-	-	
t <sub>h(SI)</sub>		Slave mode	3.5	-	-	ns
t <sub>a(SO</sub>	Data output access time	Slave mode	15	-	36	
t <sub>dis(SO)</sub>	Data output disable time	Slave mode	10	-	30	
+		Slave mode 1.65 V <v<sub>DD&lt;3.6 V</v<sub>	-	18	41	
t <sub>v(SO)</sub>	Data output valid time	Slave mode 2.7 V <v<sub>DD&lt;3.6 V</v<sub>	-	18	25	
t <sub>v(MO)</sub>		Master mode	-	4	7	
t <sub>h(SO)</sub>	Data output hold time	Slave mode	10	-	-	
t <sub>h(MO)</sub>	- Data output noid time	Master mode	0	-	-	

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> The maximum SPI clock frequency in slave transmitter mode is determined by the sum of  $t_{v(SO)}$  and  $t_{su(MI)}$  which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having  $t_{su(MI)} = 0$  while  $Duty_{(SCK)} = 50\%$ .

Table 72. SPI characteristics in voltage Range 2 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode	-		8	MHz
f <sub>SCK</sub> 1/t <sub>c(SCK)</sub>	SPI clock frequency	Slave mode Transmitter 1.65 <v<sub>DD&lt;3.6V</v<sub>		-	8	
···C(SCK)		Slave mode Transmitter 2.7 <v<sub>DD&lt;3.6V</v<sub>			8 <sup>(2)</sup>	
Duty <sub>(SCK)</sub>	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t <sub>w(SCKH)</sub>	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t <sub>su(MI)</sub>	Data input setup time	Master mode	0	-	-	
t <sub>su(SI)</sub>		Slave mode	3	-	-	
t <sub>h(MI)</sub>	Data input hold time	Master mode	11	-	-	
t <sub>h(SI)</sub>	Data input noid time	Slave mode	4.5	-	-	ns
t <sub>a(SO</sub>	Data output access time	Slave mode	18	-	52	
t <sub>dis(SO)</sub>	Data output disable time	Slave mode	12	-	42	
t <sub>v(SO)</sub>	Data output valid time	Slave mode	-	20	56.5	
t <sub>v(MO)</sub>		Master mode	-	5	9	
t <sub>h(SO)</sub>	- Data output hold time -	Slave mode	13	-	-	
t <sub>h(MO)</sub>		Master mode	3	-	-	

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> The maximum SPI clock frequency in slave transmitter mode is determined by the sum of  $t_{v(SO)}$  and  $t_{su(MI)}$  which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having  $t_{su(MI)} = 0$  while Duty<sub>(SCK)</sub> = 50%.

Table 73. SPI characteristics in voltage Range 3 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>SCK</sub>	CDI alaak fraguanay	Master mode			2	MHz
1/t <sub>c(SCK)</sub>		Slave mode	-	-	2 <sup>(2)</sup>	IVITZ
Duty <sub>(SCK)</sub>	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t <sub>w(SCKH)</sub> t <sub>w(SCKL)</sub>	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t <sub>su(MI)</sub>	Data input setup time	Master mode	1.5	-	-	
t <sub>su(SI)</sub>		Slave mode	6	-	-	
t <sub>h(MI)</sub>	Data input hold time  Data output access time	Master mode	13.5	-	-	
t <sub>h(SI)</sub>		Slave mode	16	-	-	ns
t <sub>a(SO</sub>		Slave mode	30	-	70	
t <sub>dis(SO)</sub>	Data output disable time	Slave mode	40	-	80	
t <sub>v(SO)</sub>	Data output valid time	Slave mode	-	30	70	
t <sub>v(MO)</sub>		Master mode	-	7	9	
t <sub>h(SO)</sub>	Data output hold time	Slave mode	25	-	-	
t <sub>h(MO)</sub>		Master mode	8	-	-	

<sup>1.</sup> Guaranteed by characterization results.

The maximum SPI clock frequency in slave transmitter mode is determined by the sum of t<sub>v(SO)</sub> and t<sub>su(MI)</sub> which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having t<sub>su(MI)</sub> = 0 while Duty<sub>(SCK)</sub> = 50%.

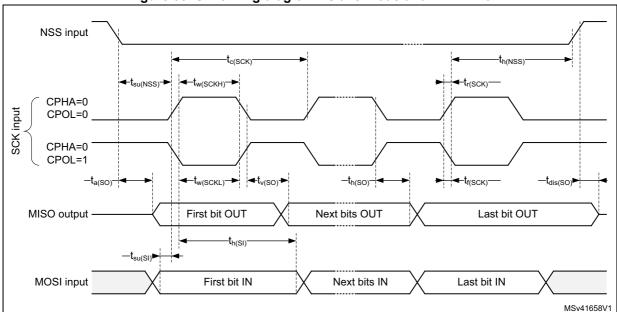
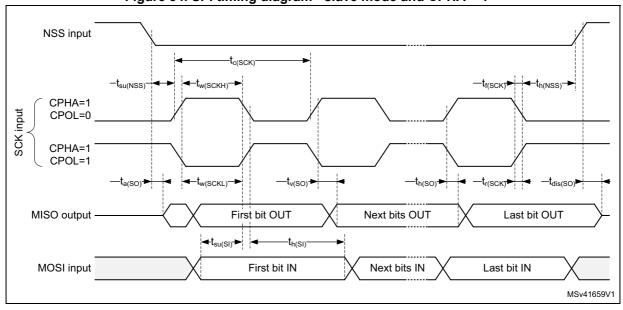


Figure 33. SPI timing diagram - slave mode and CPHA = 0

Figure 34. SPI timing diagram - slave mode and CPHA =  $1^{(1)}$ 



1. Measurement points are done at CMOS levels:  $0.3V_{DD}$  and  $0.7V_{DD}$ .

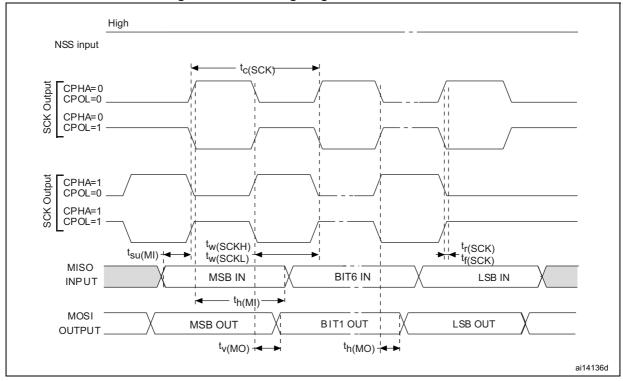


Figure 35. SPI timing diagram - master mode<sup>(1)</sup>

1. Measurement points are done at CMOS levels:  $0.3V_{DD}$  and  $0.7V_{DD}$ .



### **I2S** characteristics

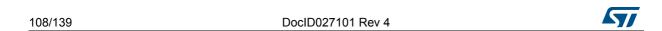
Table 74. I2S characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>MCK</sub>	I2S Main clock output	-	256 x 8K	256xFs <sup>(2)</sup>	MHz
f	I2C alook fraguanay	Master data: 32 bits	-	64xFs	MHz
f <sub>CK</sub>	I2S clock frequency	Slave data: 32 bits	-	64xFs	IVITZ
D <sub>CK</sub>	I2S clock frequency duty cycle	Slave receiver	30	70	%
t <sub>v(WS)</sub>	WS valid time	Master mode	-	15	
t <sub>h(WS)</sub>	WS hold time	Master mode	11	-	
t <sub>su(WS)</sub>	WS setup time	Slave mode	6	-	
t <sub>h(WS)</sub>	WS hold time	Slave mode	2	-	
t <sub>su(SD_MR)</sub>	Data input setup time	Master receiver	0	-	
t <sub>su(SD_SR)</sub>	Data input setup time	Slave receiver	6.5	-	ns
t <sub>h(SD_MR)</sub>	Data input hold time	Master receiver	18	-	113
t <sub>h(SD_SR)</sub>	Data input noid time	Slave receiver	15.5	-	
t <sub>v(SD_ST)</sub>	Data autout valid time	Slave transmitter (after enable edge)	-	77	
t <sub>v(SD_MT)</sub>	Data output valid time	Master transmitter (after enable edge)	-	8	
t <sub>h(SD_ST)</sub>	Data output hold time	Slave transmitter (after enable edge)	18	-	
t <sub>h(SD_MT)</sub>	Data output noid time	Master transmitter (after enable edge)	1.5	-	

<sup>1.</sup> Guaranteed by characterization results.

Note:

Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs),  $f_{MCK}$ ,  $f_{CK}$  and  $D_{CK}$  values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. DCK depends mainly on the ODD bit value, digital contribution leads to a min of (I2SDIV/(2\*I2SDIV+ODD) and a max of (I2SDIV+ODD)/(2\*I2SDIV+ODD). Fs max is supported for each mode/condition.



<sup>2. 256</sup>xFs maximum value is equal to the maximum clock frequency.

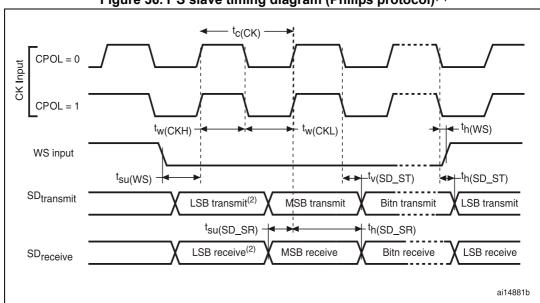


Figure 36. I<sup>2</sup>S slave timing diagram (Philips protocol)<sup>(1)</sup>

- 1. Measurement points are done at CMOS levels:  $0.3 \times V_{DD}$  and  $0.7 \times V_{DD}$ .
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

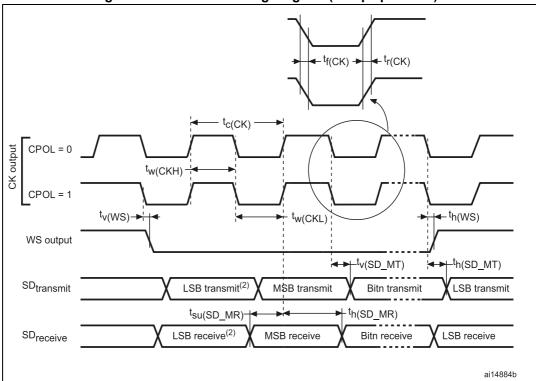


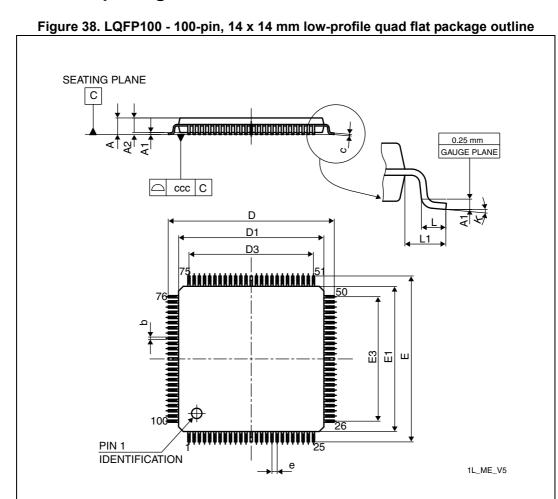
Figure 37. I<sup>2</sup>S master timing diagram (Philips protocol)<sup>(1)</sup>

- 1. Guaranteed by characterization results.
- LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

# 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status *are available at www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

## 7.1 LQFP100 package information



1. Drawing is not to scale. Dimensions are in millimeters.

Table 75. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			millimeters inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059

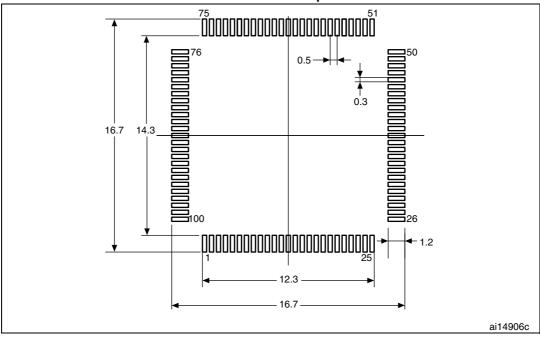


Table 75. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data (continued)

Symbol		millimeters		inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc		-	0.080	-	-	0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 39. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

### **Device marking for LQFP100**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

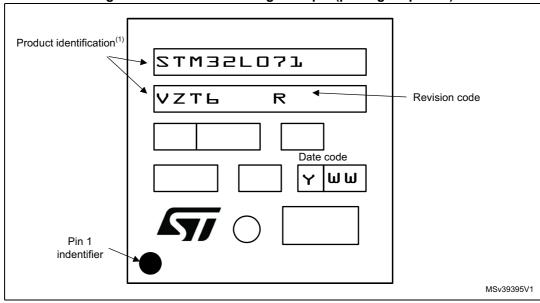
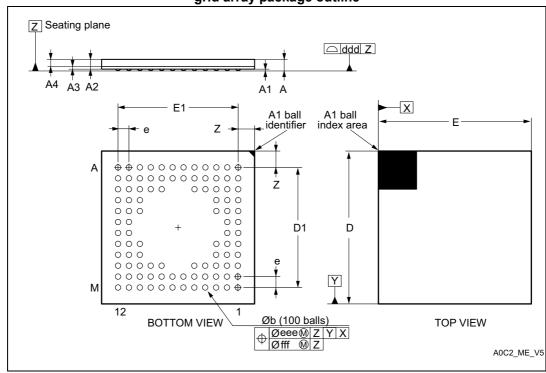


Figure 40. LQFP100 marking example (package top view)



## 7.2 UFBGA100 package information

Figure 41. UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 76. UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Comple of	millimeters				inches <sup>(1)</sup>	
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
А3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-
е	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-

Table 76. UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol .	millimeters				inches <sup>(1)</sup>	
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 42. UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package recommended footprint



Table 77. UFBGA100 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

## 7.3 LQFP64 package information

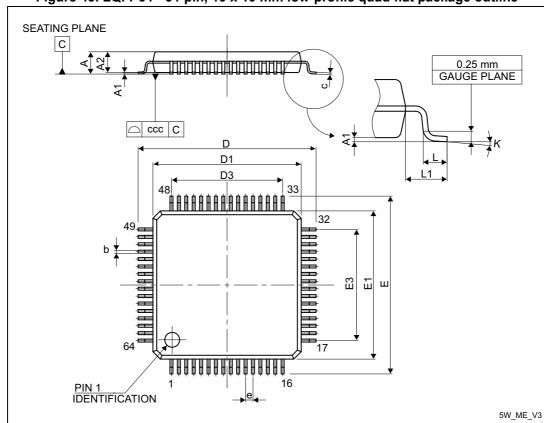


Figure 43. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 78. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data

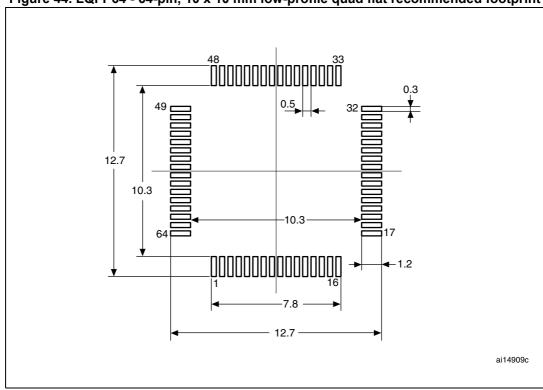
	millimeters				<u>,                                    </u>		inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max		
Α	-	-	1.600	-	-	0.0630		
A1	0.050	-	0.150	0.0020	-	0.0059		
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571		
b	0.170	0.220	0.270	0.0067	0.0087	0.0106		
С	0.090	-	0.200	0.0035	-	0.0079		
D	-	12.000	-	-	0.4724	-		
D1	-	10.000	-	-	0.3937	-		
D3	-	7.500	-	-	0.2953	-		
E	-	12.000	-	-	0.4724	-		
E1	-	10.000	-	-	0.3937	-		

Table 78. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol		millimeters		inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
E3	-	7.500	-	-	0.2953	-
е	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 44. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

#### **Device marking for LQFP64**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

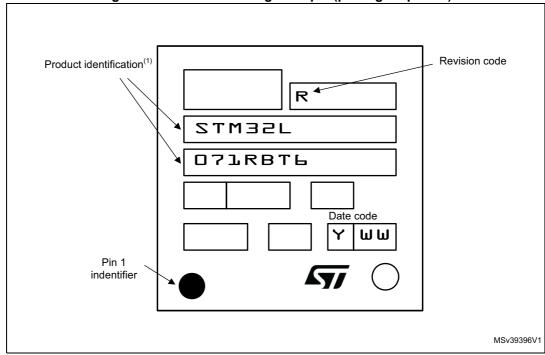
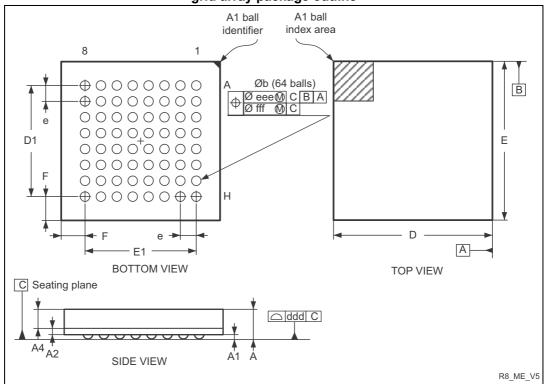


Figure 45. LQFP64 marking example (package top view)

## 7.4 TFBGA64 package information

Figure 46. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 79. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data

Cumbal	millimeters				inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
Е	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-
е	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-

Table 79. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data (continued)

millimeters			millimeters			
Symbol	Min	Тур	Max	Min	Тур	Max
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 47. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball ,grid array recommended footprint

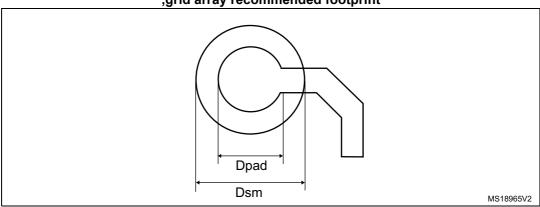


Table 80. TFBGA64 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.27 mm
Dsm	0.35 mm typ. (depends on the soldermask registration tolerance)
Solder paste	0.27 mm aperture diameter.

Note: Non solder mask defined (NSMD) pads are recommended.

4 to 6 mils solder paste screen printing process.

### **Device marking for TFBGA64**

The following figure gives an example of topside marking versus ball A 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

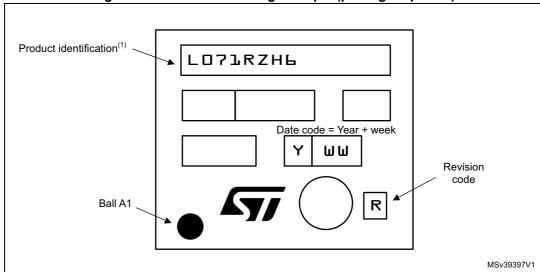
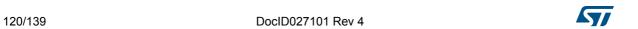
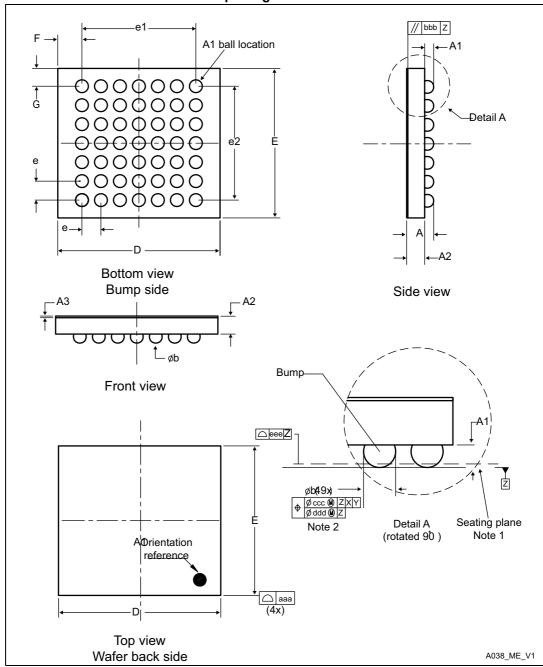


Figure 48. TFBGA64 marking example (package top view)



## 7.5 WLCSP49 package information

Figure 49. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale package outline



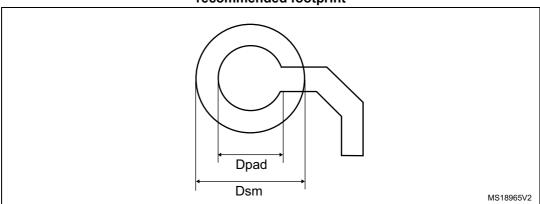
1. Drawing is not to scale.

Table 81. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol		millimeters			inches <sup>(1)</sup>	
Symbol	Min	Тур	Max	Min	Тур	Max
Α	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3 <sup>(2)</sup>	-	0.025	-	-	0.0010	-
b <sup>(3)</sup>	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.259	3.294	3.329	0.1283	0.1297	0.1311
Е	3.223	3.258	3.293	0.1269	0.1283	0.1296
е	-	0.400	-	-	0.0157	-
e1	-	2.400	-	-	0.0945	-
e2	-	2.400	-	-	0.0945	-
F	-	0.447	-	-	0.0176	-
G	-	0.429	-	-	0.0169	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

- 1. Values in inches are converted from mm and rounded to 4 decimal digits.
- 2. Back side coating
- 3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 50. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale recommended footprint





#### **Device marking for WLCSP49**

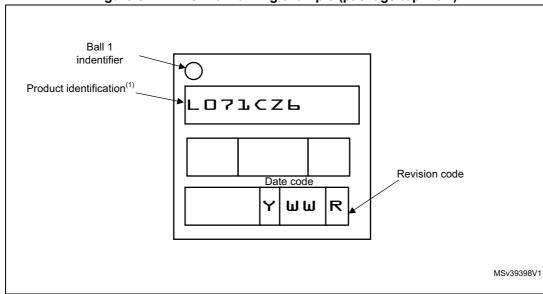
Table 82. WLCSP49 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values		
Pitch	0.4		
Dpad	260 μm max. (circular)		
рац	220 µm recommended		
Dsm	300 μm min. (for 260 μm diameter pad)		
PCB pad design	Non-solder mask defined via underbump allowed.		

The following figure gives an example of topside marking versus ball A 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 51. WLCSP49 marking example (package top view)



## 7.6 LQFP48 package information

Figure 52. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline

1. Drawing is not to scale.

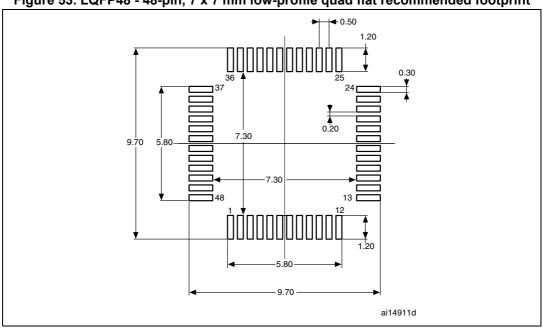


Table 83. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080			0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

#### **Device marking for LQFP48**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

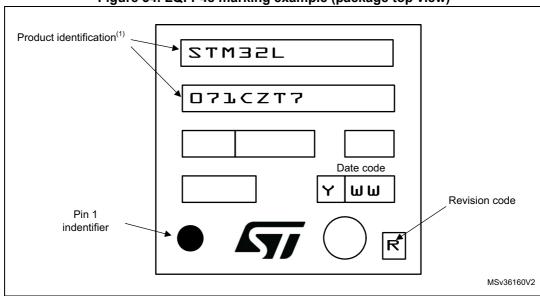


Figure 54. LQFP48 marking example (package top view)



## 7.7 LQFP32 package information

SEATING PLANE С 0.25 mm GAUGE PLANE С CCC D F D1 D3 16  $\blacksquare$ ⊞ --₩ Ш -------<del>\_\_\_\_</del>9 PIN 1 **IDENTIFICATION** 5V\_ME\_V2

Figure 55. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package outline

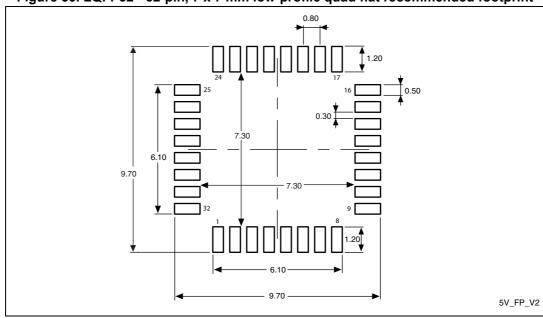
1. Drawing is not to scale.

Table 84. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.300	0.370	0.450	0.0118	0.0146	0.0177
С	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.600	-	-	0.2205	-
Е	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.600	-	-	0.2205	-
е	-	0.800	-	-	0.0315	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.100	-	-	0.0039

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 56. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

### **Device marking for LQFP32**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

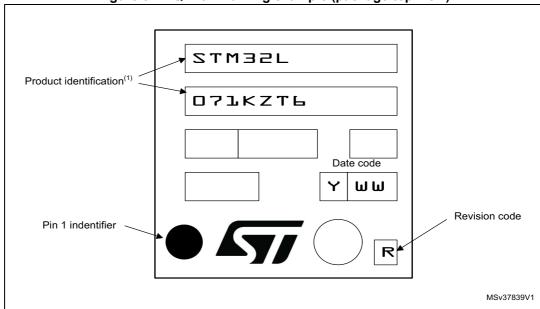
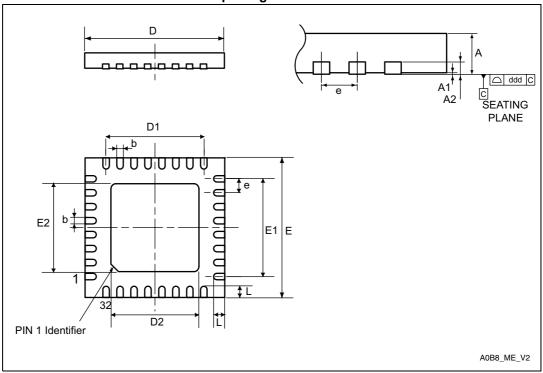


Figure 57. LQFP32 marking example (package top view)

# 7.8 UFQFPN32 package information

Figure 58. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package outline



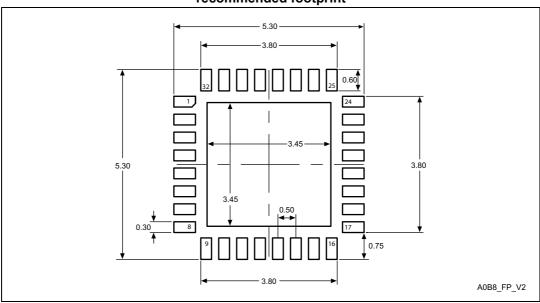
1. Drawing is not to scale.

Table 85. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
Α	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
е	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 59. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat recommended footprint



1. Dimensions are expressed in millimeters.

### **Device marking for UFQFPN32**

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

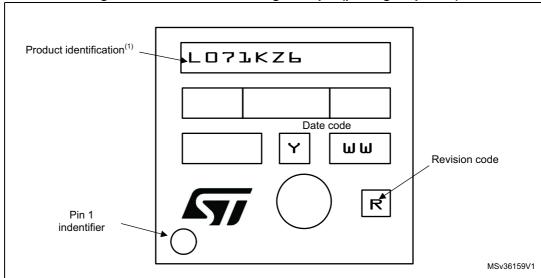


Figure 60. UFQFPN32 marking example (package top view)



## 7.9 Thermal characteristics

The maximum chip-junction temperature,  $T_J$  max, in degrees Celsius, may be calculated using the following equation:

 $T_J \max = T_A \max + (P_D \max \times \Theta_{JA})$ 

#### Where:

- T<sub>A</sub> max is the maximum ambient temperature in °C,
- Θ<sub>JA</sub> is the package junction-to-ambient thermal resistance, in ° C/W,
- $P_D$  max is the sum of  $P_{INT}$  max and  $P_{I/O}$  max ( $P_D$  max =  $P_{INT}$  max +  $P_{I/O}$ max),
- P<sub>INT</sub> max is the product of I<sub>DD</sub> and V<sub>DD</sub>, expressed in Watts. This is the maximum chip internal power.

P<sub>I/O</sub> max represents the maximum power dissipation on output pins where:

$$P_{I/O} \max = \sum (V_{OL} \times I_{OL}) + \sum ((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual  $V_{OL}$  /  $I_{OL}$  and  $V_{OH}$  /  $I_{OH}$  of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient UFQFPN32 - 5 x 5 mm / 0.5 mm pitch	36	
	Thermal resistance junction-ambient LQFP32 - 7 x 7 mm / 0.8 mm pitch	60	
	Thermal resistance junction-ambient LQFP48 - 7 x 7 mm / 0.5 mm pitch	54	
$\Theta_{JA}$	Thermal resistance junction-ambient WLCSP49 - 0.4 mm pitch	48	°C/W
OJA	Thermal resistance junction-ambient TFBGA64 - 5 x 5 mm / 0.5 mm pitch	64	0,11
	Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch	46	
	Thermal resistance junction-ambient LQFP100 - 14 x 14 mm / 0.5 mm pitch	41	
	Thermal resistance junction-ambient UFBGA100 - 7 x 7 mm / 0.5 mm pitch	57	

**Table 86. Thermal characteristics** 

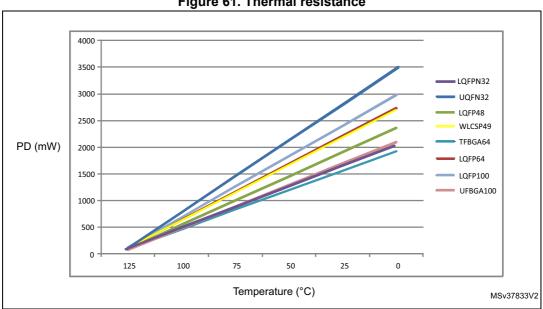


Figure 61. Thermal resistance

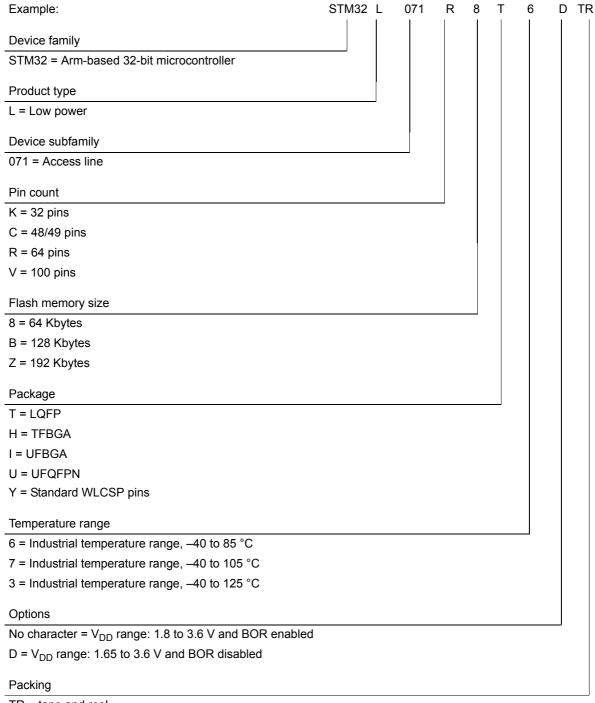
#### 7.9.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.



# 8 Ordering information

Table 87. STM32L071xx ordering information scheme



TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.



Revision history STM32L071xx

# 9 Revision history

Table 88. Document revision history

Date	Revision	Changes
02-Sep-2015	1	Initial release
26-Oct-2015	2	Changed confidentiality level to public.  Updated datasheet status to "production data".  Modified ultra-low-power platform features on cover page.  In <i>Table 15: STM32L071xxx pin definition</i> :  - changed pin name to VDDIO2 for the following pins: UFQFPN32 pin 24, LQFP48 pin 36, LQFP64 pin 48, UFBGA64 pin E5, WLCSP49 pin A1, LQFP100 pin 75 and UFBGA100 pin G11.  - Added note related to UFQFPN32.  In <i>Section 6: Electrical characteristics</i> , updated notes related to values guaranteed by characteristics, updated notes related to values guaranteed by characteristicn.  Updated  \Delta V_{SS}  definition to include V_{REF-} in <i>Table 22: Voltage characteristics</i> .  Updated f <sub>TRIG</sub> and V <sub>AIN</sub> maximum value, added V <sub>REF+</sub> and V <sub>REF-</sub> in <i>Table 62: ADC characteristics</i> .  Added <i>Section : Device marking for LQFP100</i> .  Updated <i>Figure 41: UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline</i> and <i>Table 75: LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data</i> .  Added <i>Section : Device marking for LQFP100</i> , <i>Section : Device marking for LQFP100</i> , <i>Section : Device marking for LQFP64</i> , <i>Section : Device marking for TFBGA64</i> and <i>Section : Device marking for WLCSP49</i> .

STM32L071xx Revision history

Table 88. Document revision history

Date	Revision	Changes
22-Mar-2016	3	Updated number of SPIs on cover page and in <i>Table 2: Ultra-low-power STM32L071xx device features and peripheral counts</i> .  Changed minimum comparator supply voltage to 1.65 V on cover page.  Added number of fast and standard channels in <i>Section 3.11:</i> Analog-to-digital converter (ADC).  Updated Section 3.15.2: Universal synchronous/asynchronous receiver transmitter (USART) and Section 3.15.4: Serial peripheral interface (SPI)/Inter-integrated sound (I2S) to mention the fact that USARTs with synchronous mode feature can be used as SPI master interfaces.  Added baudrate allowing to wake up the MCU from Stop mode in Section 3.15.2: Universal synchronous/asynchronous receiver transmitter (USART) and Section 3.15.3: Low-power universal asynchronous receiver transmitter (UPUART).  Changed V <sub>DDA</sub> minimum value to 1.65 V in Table 25: General operating conditions.  Section 6.3.15: 12-bit ADC characteristics:  — Table 62: ADC characteristics:  Distinction made between V <sub>DDA</sub> for fast and standard channels; added note 1.  Added note 4. related to R <sub>ADC</sub> .  Updated f <sub>TRIG</sub> and V <sub>AIN</sub> maximum value.  Updated t <sub>S</sub> and t <sub>CONV</sub> .  Added V <sub>REF+</sub> .  — Updated equation 1 description.  — Updated Table 63: RAIN max for fADC = 16 MHz for f <sub>ADC</sub> = 16 MHz and distinction made between fast and standard channels.  Added Table 87: USART/LPUART characteristics.



Revision history STM32L071xx

Table 88. Document revision history

Date	Revision	Changes
14-Sep-2017	4	Memories and I/Os moved after Core in Features.  Table 2: Ultra-low-power STM32L071xx device features and peripheral counts: changed number of USART for LQFP32/UFQFPN32 and added note 3.  Removed column "I/O operation" from Table 3: Functionalities depending on the operating power supply range and added note related to GPIO speed.  In Section 5: Memory mapping, replaced memory mapping schematic by reference to the reference manual.  Update note related to PA11/12 below Figure 3: STM32L071xx LQFP100 pinout - 14 x 14 mm, Figure 4: STM32L071xx UFBGA100 ballout - 7x 7 mm, Figure 5: STM32L071xx TFBGA64 ballout - 5x 5 mm, Figure 7: STM32L071xx WLCSP49 ballout, Figure 8: STM32L071xx UFPA48 pinout - 7 x 7 mm and Figure 10: STM32L071xx UFQFPN32 pinout.  Updated Figure 7: STM32L071xx WLCSP49 ballout.  Added mission profile compliance with JEDEC JESD47 in Section 6.2: Absolute maximum ratings.  Removed CRS from Table 39: Peripheral current consumption in Run or Sleep mode.  Updated minimum and maximum values of I/O weak pull-up equivalent resistor (R <sub>PU</sub> ) and weak pull-down equivalent resistor (R <sub>PD</sub> ) in Table 58: I/O static characteristics.  Updated minimum and maximum values of NRST weak pull-up equivalent resistor (R <sub>PU</sub> ) in Table 61: NRST pin characteristics.  Updated R <sub>AIN</sub> in Table 62: ADC characteristics.  Updated R <sub>AIN</sub> in Table 62: ADC characteristics.  Updated R <sub>AIN</sub> in Table 62: ADC characteristics.  NSS timing waveforms updated in Figure 33: SPI timing diagram - slave mode and CPHA = 0 and Figure 34: SPI timing diagram - slave mode and CPHA = 0 and Figure 34: SPI timing diagram - slave mode and CPHA = 0 and Figure 34: SPI timing diagram - slave mode and CPHA = 1(1).  Updated Figure 46: TFBGA64 - 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline.  Added reference to optional marking or inset/upset marks in all package device marking sections. Updated note below marking schematics.



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